

เอกสารอ้างอิง



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ภาคผนวก 1
ข้อมูลเกี่ยวกับไอซีเบอร์ 7400

5400/7400 Quaduple 2-Input Positive-NAND Gate

	Schottky TTL				High-Speed TTL				Low-Power Schottky TTL				Standard TTL				Low-Power TTL								
	Device Type	Package			Device Type	Package			Device Type	Package			Device Type	Package			Device Type	Package							
		C	P	M	CF		C	P	M	CF		C	P	M	CF		C	P	M	CF					
T.I.	SN54S00	J	D	N	W	SN54H00	J	D	N	W	SN54LS00	J	D	N	W	SN5400	J	D	N	W	SN54L00	J	D	N	W
	SN74S00	J	D	N	W	SN74H00	J	D	N	W	SN74LS00	J	D	N	W	SN7400	J	D	N	W	SN74L00	J	D	N	W
FAIRCHILD	FM54S00, FM9500	D	L			FM54H00, FM9H00	D	L			FM54LS00, FM9LS00	D	L			FM 5400, FM9N00	D	L							
	FC74S00, FC9300	D	L			FC74H00, FC9H00	D	L			FC74LS00, FC9LS00	D	L			FC7400, FC9N00	D	L							
MOTOROLA						MC3100	L	D							MC5400	L	D								
						MC3000	L	D			SN74LS00	P	I		MC7400	L	D								
N.S.C.	DM74S00					DM54H00	J	D			DM54LS00				DM5400	J	D				DM54L00	J	D		
						DM74H00	J	D			DM74LS00				DM7400	J	D				DM74L00	J	D		
PHILIPS	N74S00					GJH131/74H00					N74LS00				FJH131/7400										
SIGNETICS	N54S00	F	D	A	W	S54H00	F	D	A	W				SS400	F	D	A	W							
	N74S00	F	D	A	W	N74H00	F	D	A	W	N74LS00	A	I		N7400	F	D	A	W						
SIEMENS															FLH101										
FUJITSU						MB601					74LS00	M	I		MB400										
HITACHI	HD74S00										HD74LS00	P	I		HD7400/HD2503										
MITSUBISHI	M55000										M74LS00	P	I		M53200										
NEC	μPB2500										74LS00	C	I		μPB201										
TOSHIBA															TD3400 A										

Electrical Characteristics SN54LS00/SN74LS00

absolute maximum ratings over operating free-air temperature range

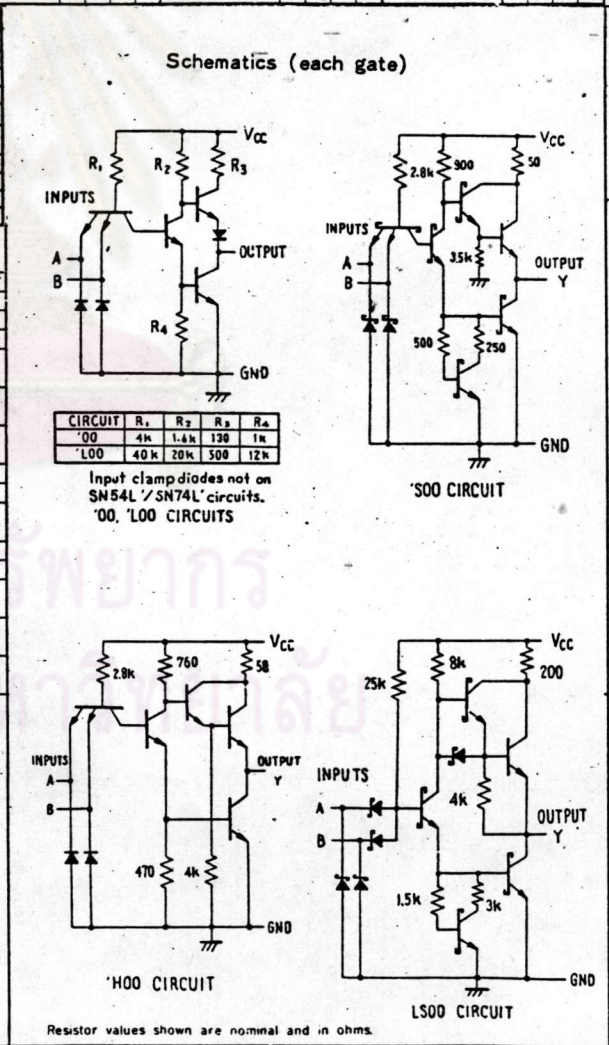
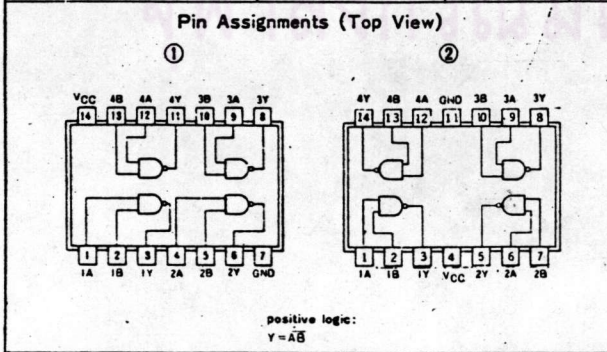
Supply voltage, V _{CC}	7V	Operating free-air temperature range	SN54LS	-55°C to 125°C
Input voltage	7V		SN74LS	0°C to 70°C
Intermittent voltage	5.5V	Storage temperature range		-65°C to 150°C

recommended operating conditions

	SN54LS00			SN74LS00			UNIT
	MIN	NOM	MAX	MIN	NOM	MAX	
Supply voltage, V _{CC}	4.5	5	5.5	4.75	5	5.25	V
High-level output current, I _{OH}			-400			-400	μA
Low-level output current, I _{OL}			4			4	mA
Operating free-air temperature, T _A	-55		125	0		70	°C

electrical characteristics over recommended operating free-air temperature range

PARAMETER	TEST CONDITIONS †	MIN	TYP ‡	MAX	UNIT	
V _{IH}	High-level input voltage		2		V	
V _{IL}	Low-level input voltage		0.8		V	
V _I	Input clamp voltage	V _{CC} =MIN, I _I =-18mA		-1.5	V	
V _{OH}	High-level output voltage	V _{CC} =MIN, V _{IL} =V _{IL} max, I _{OH} =MAX	2.7	3.4	V	
V _{OL}	Low-level output voltage	V _{CC} =MIN, V _{IH} =2V, I _{OL} =4mA	0.2	0.4	V	
I _I	Input current at maximum input voltage	V _{CC} =MAX, V _I =7V		0.1	mA	
I _{IH}	High-level input current	V _{CC} =MAX, V _{IH} =2.7V		20	μA	
I _{IL}	Low-level input current	V _{CC} =MAX, V _{IL} =0.4V		-0.4	mA	
I _{OS}	Short-circuit output current †	V _{CC} =MAX	54LS Family	-20	-100	mA
			74LS Family	-18	-100	mA
I _{CCH}	Supply current	V _{CC} =MAX	Total, outputs high	4	8	mA
I _{CCL}	Supply current		Total, outputs low	12	22	mA
I _{CC}	Supply current	V _{CC} =5V	Average per gate (50% duty cycle)	0.4		mA
t _{PLH}	Propagation delay time, low-to-high-level output	V _{CC} =5V, T _A =25°C		9	15	ns
t _{PHL}	Propagation delay time, high-to-low-level output	C _L =15pF, R _L =2kΩ		10	15	ns



† For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
‡ Typical values are at V_{CC}=5V, T_A=25°C.
• Not more than one output should be shorted at a time, and for SN54H/SN74H and SN54S/SN74S, duration of short-circuit should not exceed 1 second.

ภาคผนวก 2
ข้อมูลเกี่ยวกับไอซีเบอร์ LM339



Voltage Comparators

LM139/ 239/ 339, LM139A/239A/339A, LM2901, LM3302
Low Power Low Offset Voltage Quad Comparators
General Description

The LM139 series consists of four independent precision voltage comparators with an offset voltage specification as low as 2 mV max for all four comparators. These were designed specifically to operate from a single power supply over a wide range of voltages. Operation from split power supplies is also possible and the low power supply current drain is independent of the magnitude of the power supply voltage. These comparators also have a unique characteristic in that the input common-mode voltage range includes ground, even though operated from a single power supply voltage.

Application areas include limit comparators, simple analog to digital converters; pulse, squarewave and time delay generators; wide range VCO; MOS clock timers; multivibrators and high voltage digital logic gates. The LM139 series was designed to directly interface with TTL and CMOS. When operated from both plus and minus power supplies, they will directly interface with MOS logic— where the low power drain of the LM339 is a distinct advantage over standard comparators.

Advantages

- High precision comparators
- Reduced V_{OS} drift over temperature

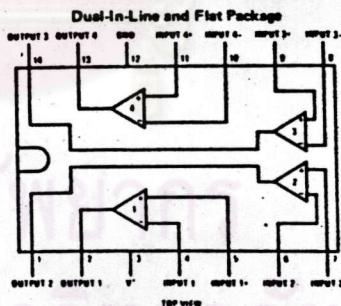
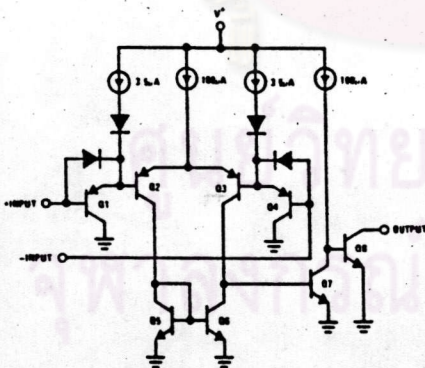
- Eliminates need for dual supplies
- Allows sensing near gnd
- Compatible with all forms of logic
- Power drain suitable for battery operation

Features

- Wide single supply voltage range or dual supplies
 - LM139 series, 2 VDC to 36 VDC or
 - LM139A series, LM2901 ± 1 VDC to ± 18 VDC
 - LM3302 2 VDC to 28 VDC or ± 1 VDC to ± 14 VDC
- Very low supply current drain (0.8 mA) – independent of supply voltage (2 mW/comparator at +5 VDC)
- Low input biasing current 25 nA
- Low input offset current ± 5 nA and offset voltage ± 3 mV
- Input common-mode voltage range includes gnd
- Differential input voltage range equal to the power supply voltage
- Low output 250 mV at 4 mA saturation voltage
- Output voltage compatible with TTL, DTL, ECL, MOS and CMOS logic systems

LM139/LM239/LM339,
LM139A/LM239A/LM339A, LM2901, LM3302

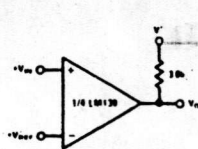
Schematic and Connection Diagrams



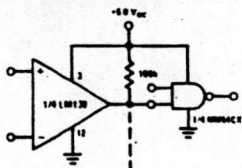
Order Number LM139J, LM139AJ,
LM239J, LM239AJ, LM339J,
LM339AJ, LM2901J or LM3302J
See NS Package J14A

Order Number LM339N, LM339AN,
LM2901N or LM3302N
See NS Package N14A

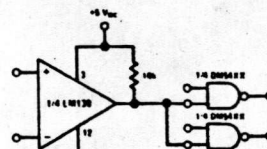
Typical Applications ($V^+ = 5.0$ VDC)



Basic Comparator



Driving CMOS



Driving TTL

LM139/LM239/LM339, LM139A/LM239A/LM339A, LM2901, LM3302

Absolute Maximum Ratings

	LM139/LM239/LM339 LM139A/LM239A/LM339A LM2901	LM3302
Supply Voltage, V^+	36 VDC or ± 18 VDC	28 VDC or ± 14 VDC
Differential Input Voltage	36 VDC	28 VDC
Input Voltage	-0.3 VDC to +36 VDC	-0.3 VDC to +28 VDC
Power Dissipation (Note 1)		
Molded DIP	570 mW	570 mW
Cavity DIP	900 mW	
Flat Pack	800 mW	
Output Short-Circuit to GND, (Note 2)	Continuous	Continuous
Input Current ($V_{IN} < -0.3$ VDC), (Note 3)	50 mA	50 mA
Operating Temperature Range		
LM339A	0°C to +70°C	-40°C to +85°C
LM239A	-25°C to +85°C	
LM2901	-40°C to +85°C	
LM139A	-55°C to +125°C	
Storage Temperature Range	-65°C to +150°C	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C	300°C

Electrical Characteristics ($V^+ = 5$ VDC, Note 4)

PARAMETER	CONDITIONS	LM139A			LM239A, LM339A			LM139			LM239, LM339			LM2901			LM3302			UNITS	
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX		
Input Offset Voltage	$T_A = 25^\circ\text{C}$, (Note 9)		± 1.0	± 2.0		± 1.0	± 2.0		± 2.0	± 5.0		± 2.0	± 5.0		± 2.0	± 7.0		± 3	± 20	mVDC	
Input Bias Current	$I_{IN(+)}$ or $I_{IN(-)}$ with Output in Linear Range, $T_A = 25^\circ\text{C}$, (Note 5)		25	100		25	250		25	100		25	250		25	250		25	500	nADC	
Input Offset Current	$I_{IN(+)} - I_{IN(-)}$, $T_A = 25^\circ\text{C}$		± 3.0	± 25		± 5.0	± 50		± 3.0	± 25		± 5.0	± 50		± 5	± 50		± 3	± 100	nADC	
Input Common-Mode Voltage Range	$T_A = 25^\circ\text{C}$, (Note 6)	0		$V^+ - 1.5$	0		$V^+ - 1.5$	0		$V^+ - 1.5$	0		$V^+ - 1.5$	0		$V^+ - 1.5$	0		$V^+ - 1.5$	VDC	
Supply Current	$R_L = \infty$ on all Comparators, $T_A = 25^\circ\text{C}$ $R_L = \infty$, $V^+ = 30\text{V}$, $T_A = 25^\circ\text{C}$		0.8	2.0		0.8	2.0		0.8	2.0		0.8	2.0		0.8	2.0		0.8	2	mADC	
Voltage Gain	$R_L \geq 15\text{ k}\Omega$, $V^+ = 15\text{ VDC}$ (To Support Large V_O Swing), $T_A = 25^\circ\text{C}$	50	200		50	200		200		200		25	100		2	30					V/mV
Large Signal Response Time	$V_{IN} = \text{TTL Logic Swing}$, $V_{REF} = 1.4\text{ VDC}$, $V_{RL} = 5\text{ VDC}$, $R_L = 5.1\text{ k}\Omega$, $T_A = 25^\circ\text{C}$		300		300		300		300		300		300		300		300				ns
Response Time	$V_{RL} = 5\text{ VDC}$, $R_L = 5.1\text{ k}\Omega$, $T_A = 25^\circ\text{C}$, (Note 7)		1.3		1.3		1.3		1.3		1.3		1.3		1.3		1.3				μs
Output Sink Current	$V_{IN(-)} \geq 1\text{ VDC}$, $V_{IN(+)} = 0$, $V_O \leq 1.5\text{ VDC}$, $T_A = 25^\circ\text{C}$	6.0	16		6.0	16		6.0	16		6.0	16		6.0	16		6.0	16		16	mADC
Saturation Voltage	$V_{IN(-)} \geq 1\text{ VDC}$, $V_{IN(+)} = 0$, $I_{SINK} \leq 4\text{ mA}$, $T_A = 25^\circ\text{C}$		250	400		250	400		250	400		250	400		400		250	500			mVDC
Output Leakage Current	$V_{IN(+)} \geq 1\text{ VDC}$, $V_{IN(-)} = 0$, $V_O = 5\text{ VDC}$, $T_A = 25^\circ\text{C}$		0.1		0.1		0.1		0.1		0.1		0.1		0.1		0.1				nADC

Electrical Characteristics (Continued)

PARAMETER	CONDITIONS	LM139A			LM239A, LM339A			LM139			LM239, LM339			LM2901			LM3302			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
Input Offset Voltage	(Note 9)			4.0			4.0			9.0			9.0	9	15				40	mVDC
Input Offset Current	$I_{IN(+)} - I_{IN(-)}$			±100			±150			±100			±150	50	200				300	nADC
Input Bias Current	$I_{IN(+)}$ or $I_{IN(-)}$ with Output in Linear Range			300			400			300			400	200	500				1000	nADC
Input Common-Mode Voltage Range		0		$V^+ - 2.0$	0		$V^+ - 2.0$	0		$V^+ - 2.0$	0		$V^+ - 2.0$	0		$V^+ - 2.0$	0		$V^+ - 2.0$	VDC
Saturation Voltage	$V_{IN(-)} \geq 1 \text{ VDC}$, $V_{IN(+)} = 0$, $I_{SINK} \leq 4 \text{ mA}$			700			700			700			700	400	700				700	mVDC
Output Leakage Current	$V_{IN(+)} \geq 1 \text{ VDC}$, $V_{IN(-)} = 0$, $V_O = 30 \text{ VDC}$			1.0			1.0			1.0			1.0	1.0					1.0	µADC
Differential Input Voltage	Keep all V_{IN} 's $\geq 0 \text{ VDC}$ (or V^- , if used), (Note 8)			36			36			36			36	0	36				28	VDC

Note 1: For operating at high temperatures, the LM339/LM339A, LM2901, LM3302 must be derated based on a 125°C maximum junction temperature and a thermal resistance of 175°C/W which applies for the device soldered in a printed circuit board, operating in a still air ambient. The LM239 and LM139 must be derated based on a 150°C maximum junction temperature. The low bias dissipation and the "ON-OFF" characteristic of the outputs keeps the chip dissipation very small ($P_D \leq 100 \text{ mW}$), provided the output transistors are allowed to saturate.

Note 2: Short circuits from the output to V^+ can cause excessive heating and eventual destruction. The maximum output current is approximately 20 mA independent of the magnitude of V^+ .

Note 3: This input current will only exist when the voltage at any of the input leads is driven negative. It is due to the collector-base junction of the input PNP transistors becoming forward biased and thereby acting as input diode clamps. In addition to this diode action, there is also lateral NPN parasitic transistor action on the IC chip. This transistor action can cause the output voltages of the comparators to go to the V^+ voltage level (or to ground for a large overdrive) for the time duration that an input is driven negative. This is not destructive and normal output states will re-establish when the input voltage, which was negative, again returns to a value greater than -0.3 VDC (at 25°C).

Note 4: These specifications apply for $V^+ = 5 \text{ VDC}$ and $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$, unless otherwise stated. With the LM239/LM239A, all temperature specifications are limited to $-25^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$, the LM339/LM339A temperature specifications are limited to $0^\circ\text{C} \leq T_A \leq +70^\circ\text{C}$, and the LM2901, LM3302 temperature range is $-40^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$.

Note 5: The direction of the input current is out of the IC due to the PNP input stage. This current is essentially constant, independent of the state of the output so no loading change exists on the reference or input lines.

Note 6: The input common-mode voltage or either input signal voltage should not be allowed to go negative by more than 0.3V. The upper end of the common-mode voltage range is $V^+ - 1.5\text{V}$, but either or both inputs can go to $+30 \text{ VDC}$ without damage (25V for LM3302).

Note 7: The response time specified is a 100 mV input step with 5 mV overdrive. For larger overdrive signals 300 ns can be obtained, see typical performance characteristics section.

Note 8: Positive excursions of input voltage may exceed the power supply level. As long as the other voltage remains within the common-mode range, the comparator will provide a proper output state. The low input voltage state must not be less than -0.3 VDC (or 0.3 VDC below the magnitude of the negative power supply, if used) (at 25°C).

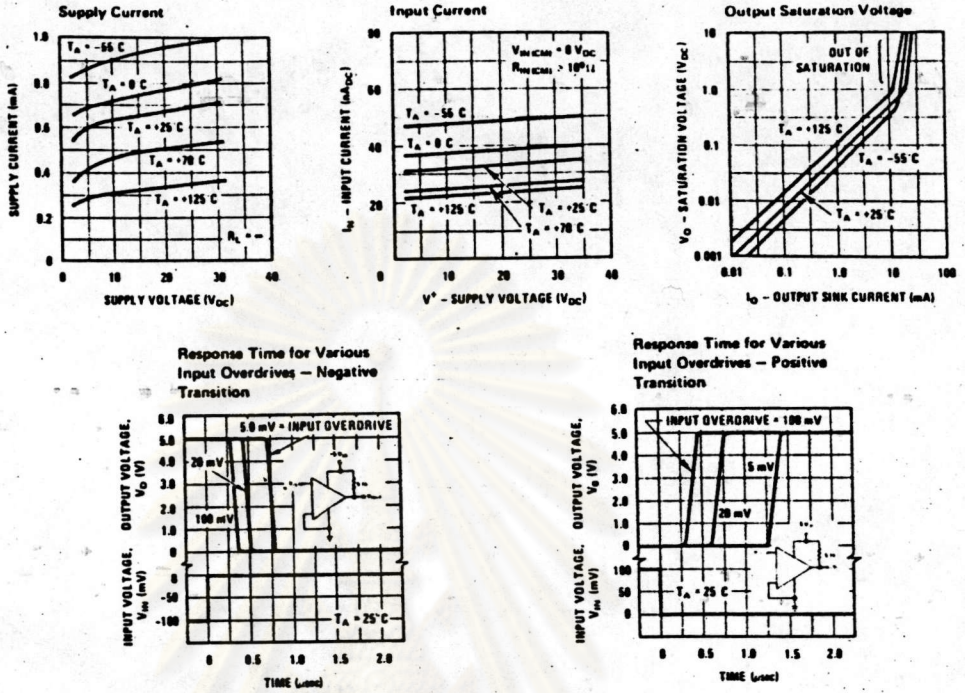
Note 9: At output switch point, $V_O = 1.4 \text{ VDC}$, $R_S = 0\Omega$ with V^+ from 5 VDC ; and over the full input common-mode range (0 VDC to $V^+ - 1.5 \text{ VDC}$).

ศูนย์วิทยุพัชกร
จุฬาลงกรณ์มหาวิทยาลัย

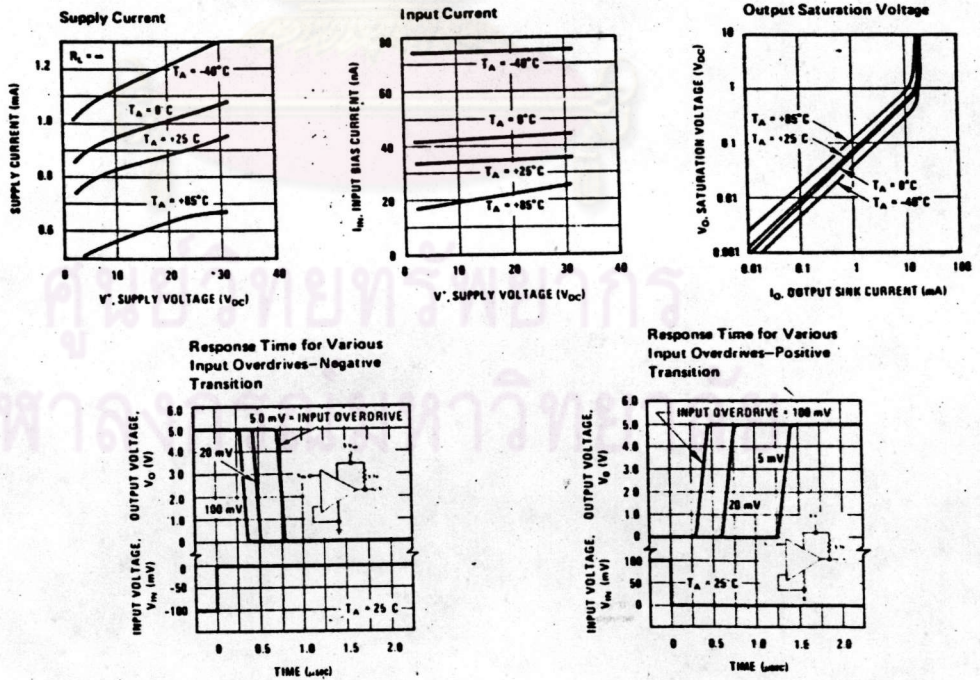
LM139/LM239/LM339, LM2901, LM3302, LM139A/LM239A/LM339A

LM139/LM239/LM339, LM2901, LM3302
LM139A/LM239A/LM339A, LM2901A, LM3302A

Typical Performance Characteristics LM139/LM239/LM339, LM139A/LM239A/LM339A, LM3302



Typical Performance Characteristics LM2901



ภาคผนวก 3
ข้อมูลเกี่ยวกับไอซีเบอร์ 74121

54121/74121 Monostable Multivibrator with Schmitt-Trigger Input

	Schottky TTL				High-Speed TTL				Low-Power Schottky TTL				Standard TTL				Low-Power TTL				
	Device Type	Package			Device Type	Package			Device Type	Package			Device Type	Package			Device Type	Package			
		C	P	M	CF		C	P	M	CF		C	P	M	CF		C	P	M	CF	
TI												SN54121	J1			W1	SN54L121	J1	N1	T1	
												SN74121	J1	N1	T1		SN74L121	J1	N1	T1	
FAIRCHILD												FM54121	F	M	603	F1					
												FC74121	F	C	603	F1					
MOTOROLA												MCS4121	L	C		F1					
												MC74121	L	C		F1					
N.S.C.												DM54121	J	M		W1					
												DM74121	J	M		W1					
PHILIPS																					
												FJK101/74121									
SIGNETICS												SS4121	F	T		W1					
												N74121	F	D		W1					
SIEMENS																					
												FLK101									
FUJITSU																					
HTACHI																					
												HD74121/HD2543									
MITSUBISHI																					
												M53321									
NEC																					
TOSHIBA																					
												TD3121A									

Electrical Characteristics SN54S121 SN74S121					
absolute maximum ratings over operating free-air temperature range					
supply voltage V _{CC}	5.5				
input voltage	5.5				
output voltage	5.5				
output current I _{OL}	16				
storage temperature range	-55 to 125				
recommended operating conditions					
SN54S121 SN74S121 UNIT					
supply voltage V _{CC}	MIN NOM MAX				
high-level output current I _{OH}	MIN NOM MAX				
low-level output current I _{OL}	MIN NOM MAX				
propagation delay t _{PLH}	MIN NOM MAX				
propagation delay t _{PHL}	MIN NOM MAX				
rise time t _r	MIN NOM MAX				
fall time t _f	MIN NOM MAX				
settle time t _s	MIN NOM MAX				
output delay t _{OD}	MIN NOM MAX				
output delay t _{OD}	MIN NOM MAX				
operating free-air temperature T _A	MIN NOM MAX				
electrical characteristics over recommended operating free-air temperature range					
PARAMETER	TEST CONDITIONS †	MIN	TYP ‡	MAX	UNIT
V _{T+} Positive-going threshold voltage	V _{CC} - MIN, A input	1.4	1.4	2	V
V _{T-} Negative-going threshold voltage	V _{CC} - MIN, A input	0.8	1.4	2	V
V _{T+} Positive-going threshold voltage	V _{CC} - MIN, B input	1.55	1.55	2	V
V _{T-} Negative-going threshold voltage	V _{CC} - MIN, B input	0.8	1.35	2	V
V _I Input clamp voltage	V _{CC} - MIN, I _I = -12mA	1.5	1.5	1.5	V
V _{OH} High-level output voltage	V _{CC} - MIN, I _{OH} = MAX	2.4	3.4	5	V
V _{OL} Low-level output voltage	V _{CC} - MIN, I _{OL} = MAX	0.2	0.4	0.4	V
I _I Input current at maximum input voltage	V _{CC} - MAX, V _I = 5.5V	1	1	1	mA
I _{IH} High-level input current	V _{CC} - MAX, V _I = 2.4V, A1 or A2	2	40	80	μA
I _{IH} High-level input current	V _{CC} - MAX, V _I = 2.4V, B	1.6	1.6	1.6	μA
I _{IL} Low-level input current	V _{CC} - MAX, V _I = 0.4V, A1 or A2	3.2	3.2	3.2	mA
I _{OS} Short-circuit output current *	V _{CC} - MAX, Quiescent	20	55	55	mA
I _{OS} Short-circuit output current *	V _{CC} - MAX, Triggered	18	25	25	mA
I _{CC} Supply current	V _{CC} - MAX	13	13	25	mA
t _{PLH} Propagation delay time, low-to-high-level Q output from either A input	V _{CC} = 5V, T _A = 25°C, C _T = 80 pF, R _{int} to V _{CC}	45	70	70	ns
t _{PLH} Propagation delay time, low-to-high-level Q output from B input	V _{CC} = 5V, T _A = 25°C, C _T = 80 pF, R _{int} to V _{CC}	35	55	55	ns
t _{PHL} Propagation delay time, high-to-low-level Q output from either A input	V _{CC} = 5V, T _A = 25°C, C _T = 80 pF, R _{int} to V _{CC}	50	80	80	ns
t _{PHL} Propagation delay time, high-to-low-level Q output from B input	V _{CC} = 5V, T _A = 25°C, C _T = 80 pF, R _{int} to V _{CC}	40	65	65	ns
t _{w(out)} Pulse width obtained using internal timing resistor	V _{CC} = 5V, T _A = 25°C, C _T = 0, R _{int} to V _{CC}	70	110	150	ns
t _{w(out)} Pulse width obtained with zero timing capacitance	V _{CC} = 5V, T _A = 25°C, C _T = 0, R _{int} to V _{CC}	30	50	50	ns
t _{w(out)} Pulse width obtained using external timing resistor	C _T = 100 pF, R _T = 10 kΩ, C _T = 1 μF, R _T = 10 kΩ	600	700	800	ns
t _{w(out)} Pulse width obtained using external timing resistor	C _T = 1 μF, R _T = 10 kΩ	6	7	8	ms

Pin Assignment (Top view)

NC-No internal connection
 †21...R_{int} = 2 kΩ NOM
 †121...R_{int} = 4 kΩ NOM

Function Table
 †21... †121 (See Note)

INPUTS		OUTPUTS	
A1	A2	B	Q
L	X	H	L
X	L	H	L
X	X	L	L
H	H	X	L
H	L	H	L
L	X	H	L
X	L	H	L

Schematics of inputs and outputs

EQUIVALENT OF EACH INPUT
 A1 4 kΩ, A2 4 kΩ, B 2 kΩ

TYPICAL OF BOTH OUTPUTS
 †21 R_{int} = 2 kΩ NOM, †121 R_{int} = 4 kΩ NOM

NOTES:
 A H = high level (steady state), L = low level (steady state), ↑ = transition from low to high level, ↓ = transition from high to low level, ↑L = one high-level pulse, ↓L = one low-level pulse, X = irrelevant (any input, including transitions)
 B To use the internal timing resistor connect R_{int} to V_{CC}.
 C An external timing capacitor may be connected between C_{ext} (positive) and R_{ext}/C_{ext}.
 D For accurate repeatable pulse widths, connect an external resistor between R_{ext}/C_{ext} and V_{CC} with R_{int} open-circuited.
 E To obtain variable pulse widths, connect external values resistance between R_{int} or R_{ext}/C_{ext} and V_{CC}.

† For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
 ‡ All typical values are at V_{CC} = 5V, T_A = 25°C.
 * Not more than one output should be driven at a time.



Voltage Comparators

LM311 Voltage Comparator

General Description

The LM311 is a voltage comparator that has input currents more than a hundred times lower than devices like the LM306 or LM710C. It is also designed to operate over a wider range of supply voltages: from standard $\pm 15V$ op amp supplies down to the single 5V supply used for IC logic. Its output is compatible with RTL, DTL and TTL as well as MOS circuits. Further, it can drive lamps or relays, switching voltages up to 40V at currents as high as 50 mA.

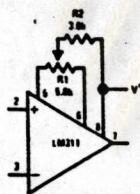
- Differential input voltage range: $\pm 30V$
- Power consumption: 135 mW at $\pm 15V$

Both the input and the output of the LM311 can be isolated from system ground, and the output can drive loads referred to ground, the positive supply or the negative supply. Offset balancing and strobe capability are provided and outputs can be wire OR'ed. Although slower than the LM306 and LM710C (200 ns response time vs 40 ns) the device is also much less prone to spurious oscillations. The LM311 has the same pin configuration as the LM306 and LM710C. See the "application hints" of the LM311 for application help.

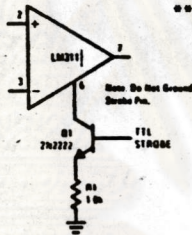
Features

- Operates from single 5V supply
- Maximum input current: 250 nA
- Maximum offset current: 50 nA

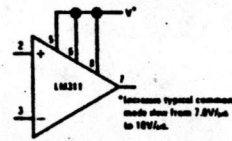
Auxiliary Circuits **



Offset Balancing



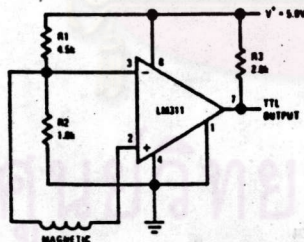
Strobing



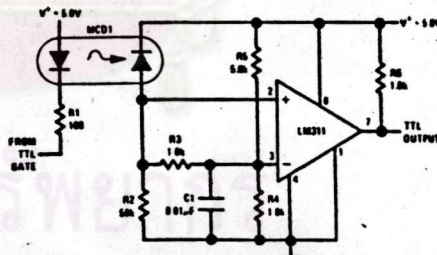
Increasing Input Stage Current*

** Note: Pin connections shown on schematic diagram and typical applications are for TO-5 package.

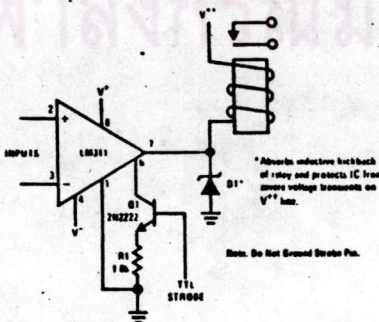
Typical Applications **



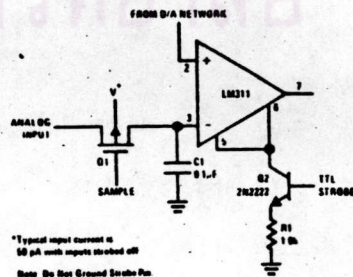
Detector for Magnetic Transducer



Digital Transmission Isolator



Relay Driver with Strobe



Strobing off Both Input and Output Stages

Absolute Maximum Ratings

Total Supply Voltage (V_{S+})	36V
Output to Negative Supply Voltage (V_{7+})	40V
Ground to Negative Supply Voltage (V_{1+})	30V
Differential Input Voltage	$\pm 30V$
Input Voltage (Note 1)	$\pm 15V$
Power Dissipation (Note 2)	500 mW
Output Short Circuit Duration	10 sec
Operating Temperature Range	$0^{\circ}C$ to $70^{\circ}C$
Storage Temperature Range	$-65^{\circ}C$ to $150^{\circ}C$
Lead Temperature (soldering, 10 sec)	$300^{\circ}C$
Voltage at Strobe Pin	$V^{+}-5V$

Electrical Characteristics (Note 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
Input Offset Voltage (Note 4)	$T_A = 25^{\circ}C, R_S \leq 50k$		2.0	7.5	mV
Input Offset Current (Note 4)	$T_A = 25^{\circ}C$		6.0	50	nA
Input Bias Current	$T_A = 25^{\circ}C$		100	250	nA
Voltage Gain	$T_A = 25^{\circ}C$	40	200		V/mV
Response Time (Note 5)	$T_A = 25^{\circ}C$		200		ns
Saturation Voltage	$V_{IN} \leq -10$ mV, $I_{OUT} = 50$ mA $T_A = 25^{\circ}C$		0.75	1.5	V
Strobe ON Current	$T_A = 25^{\circ}C$		3.0		mA
Output Leakage Current	$V_{IN} \geq 10$ mV, $V_{OUT} = 35V$ $T_A = 25^{\circ}C, I_{STROBE} = 3$ mA		0.2	50	nA
Input Offset Voltage (Note 4)	$R_S \leq 50k$			10	mV
Input Offset Current (Note 4)				70	nA
Input Bias Current				300	nA
Input Voltage Range		-14.5	13.8-14.7	13.0	V
Saturation Voltage	$V^{+} \geq 4.5V, V^{-} = 0$ $V_{IN} \leq -10$ mV, $I_{SINK} \leq 8$ mA		0.23	0.4	V
Positive Supply Current	$T_A = 25^{\circ}C$		5.1	7.5	mA
Negative Supply Current	$T_A = 25^{\circ}C$		4.1	5.0	mA

Note 1: This rating applies for $\pm 15V$ supplies. The positive input voltage limit is 30V above the negative supply. The negative input voltage limit is equal to the negative supply voltage or 30V below the positive supply, whichever is less.

Note 2: The maximum junction temperature of the LM311 is $110^{\circ}C$. For operating at elevated temperatures, devices in the TO-5 package must be derated based on a thermal resistance of $150^{\circ}C/W$, junction to ambient, or $45^{\circ}C/W$, junction to case. The thermal resistance of the dual-in-line package is $100^{\circ}C/W$, junction to ambient.

Note 3: These specifications apply for $V_S = \pm 15V$ and the Ground pin at ground, and $0^{\circ}C < T_A < +70^{\circ}C$, unless otherwise specified. The offset voltage, offset current and bias current specifications apply for any supply voltage from a single 5V supply up to $\pm 15V$ supplies.

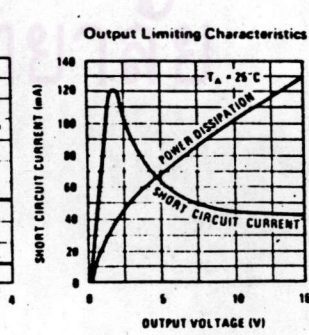
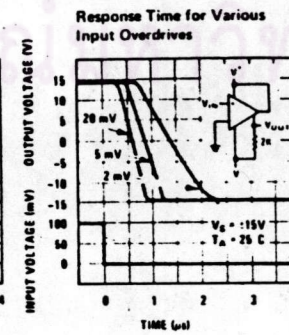
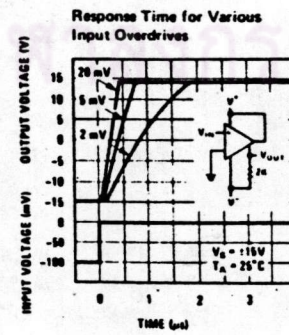
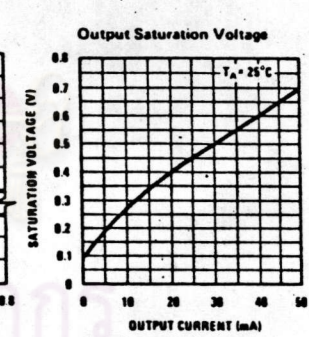
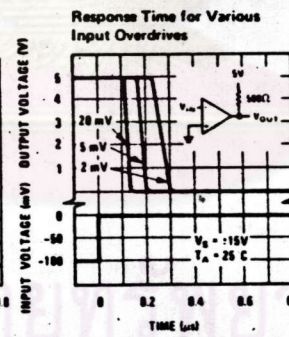
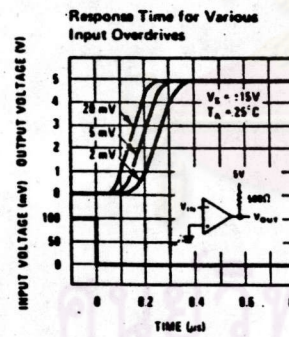
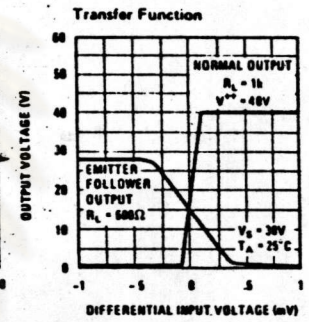
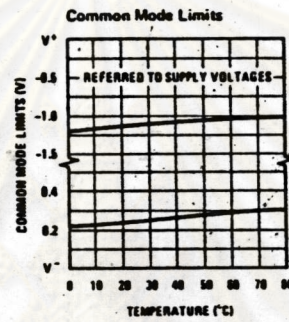
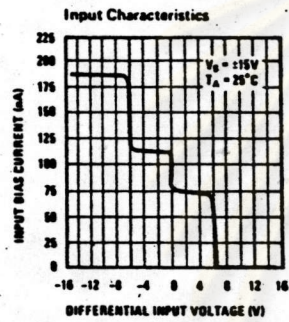
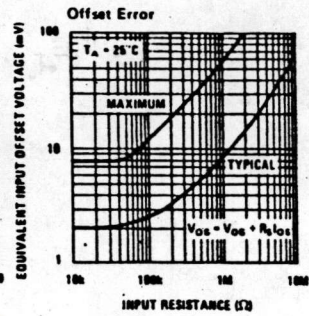
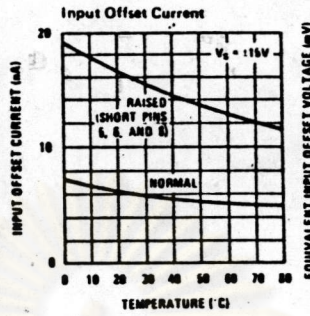
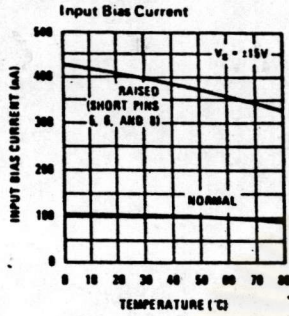
Note 4: The offset voltages and offset currents given are the maximum values required to drive the output within a volt of either supply with 1 mA load. Thus, these parameters define an error band and take into account the worst-case effects of voltage gain and input impedance.

Note 5: The response time specified (see definitions) is for a 100 mV input step with 5 mV overdrive.

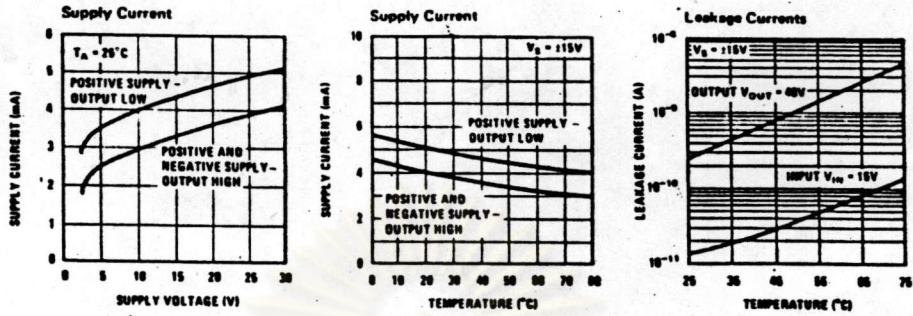
Note 6: Do not short the strobe pin to ground; it should be current driven at 3 to 5 mA.

LM311

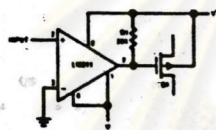
Typical Performance Characteristics



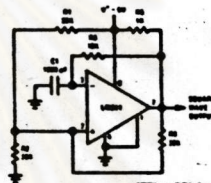
Typical Performance Characteristics (Continued)



Typical Applications

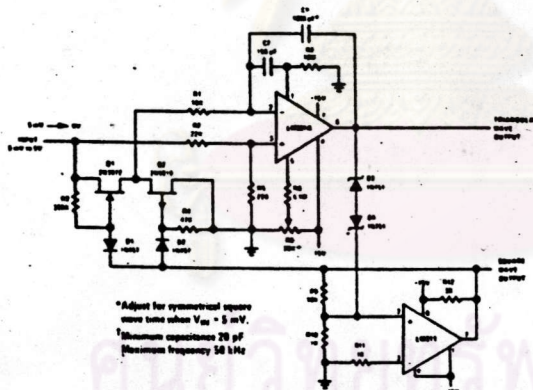


Zero Crossing Detector Driving MOS Switch



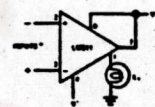
100 kHz Free Running Multivibrator

*TTL or TTL format of time.



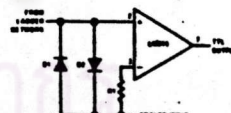
10 Hz to 10 kHz Voltage Controlled Oscillator

*Adjust for symmetrical square wave tone when $V_{in} = 5\text{ mV}$.
 †Maximum capacitance 20 pF
 ‡Maximum frequency 50 kHz

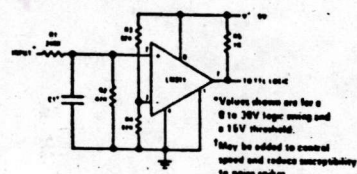


Driving Ground-Referred Load

*Input polarity is reversed when using pin 1 as output.

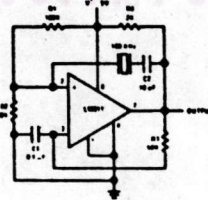


Using Clamp Diodes to Improve Response

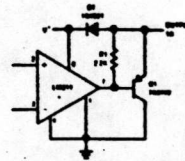


TTL Interface with High Level Logic

*Values shown are for a 0 to 20V logic swing and a 15V threshold.
 †May be added to control speed and reduce susceptibility to noise spikes.



Crystal Oscillator



Comparator and Solenoid Driver



Silicon Gate MOS 8255

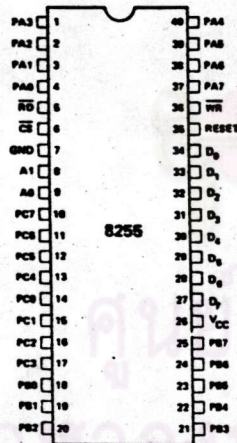
PROGRAMMABLE PERIPHERAL INTERFACE

- 24 Programmable I/O Pins
- Completely TTL Compatible
- Fully Compatible with MCS™-8 and MCS™-80 Microprocessor Families
- Direct Bit Set/Reset Capability Easing Control Application Interface
- 40 Pin Dual In-Line Package
- Reduces System Package Count

The 8255 is a general purpose programmable I/O device designed for use with both the 8008 and 8080 microprocessors. It has 24 I/O pins which may be individually programmed in two groups of twelve and used in three major modes of operation. In the first mode (Mode 0), each group of twelve I/O pins may be programmed in sets of 4 to be input or output. In Mode 1, the second mode, each group may be programmed to have 8 lines of input or output. Of the remaining four pins three are used for handshaking and interrupt control signals. The third mode of operation (Mode 2) is a Bidirectional Bus mode which uses 8 lines for a bidirectional bus, and five lines, borrowing one from the other group, for handshaking.

Other features of the 8255 include bit set and reset capability and the ability to source 1mA of current at 1.5 volts. This allows darlington transistors to be directly driven for applications such as printers and high voltage displays.

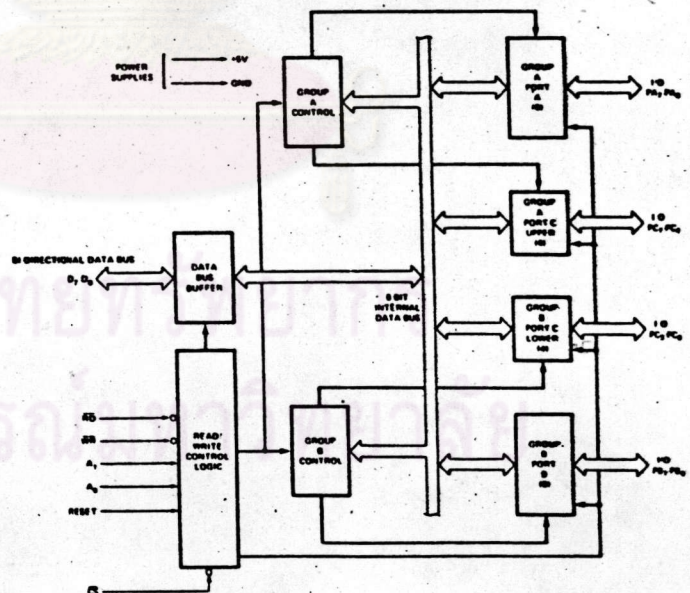
PIN CONFIGURATION



PIN NAMES

D ₇ -D ₀	DATA BUS (BI-DIRECTIONAL)
RESET	RESET INPUT
CS	CHIP SELECT
RD	READ INPUT
WR	WRITE INPUT
A0, A1	PORT ADDRESS
PA7-PA0	PORT A (BIT)
PB7-PB0	PORT B (BIT)
PC7-PC0	PORT C (BIT)
V _{CC}	+5 VOLTS
GND	0 VOLTS

8255 BLOCK DIAGRAM



SILICON GATE MOS 8255

8255 BASIC FUNCTIONAL DESCRIPTION

General

The 8255 is a Programmable Peripheral Interface (PPI) device designed for use in 8080 Microcomputer Systems. Its function is that of a general purpose I/O component to interface peripheral equipment to the 8080 system bus. The functional configuration of the 8255 is programmed by the system software so that normally no external logic is necessary to interface peripheral devices or structures.

Data Bus Buffer

This 3-state, bi-directional, eight bit buffer is used to interface the 8255 to the 8080 system data bus. Data is transmitted or received by the buffer upon execution of INput or OUTput instructions by the 8080 CPU. Control Words and Status information are also transferred through the Data Bus buffer.

Read/Write and Control Logic

The function of this block is to manage all of the internal and external transfers of both Data and Control or Status words. It accepts inputs from the 8080 CPU Address and Control busses and in turn, issues commands to both of the Control Groups.

(CS)

Chip Select: A "low" on this input pin enables the communication between the 8255 and the 8080 CPU.

(RD)

Read: A "low" on this input pin enables the 8255 to send the Data or Status information to the 8080 CPU on the Data Bus. In essence, it allows the 8080 CPU to "read from" the 8255.

(WR)

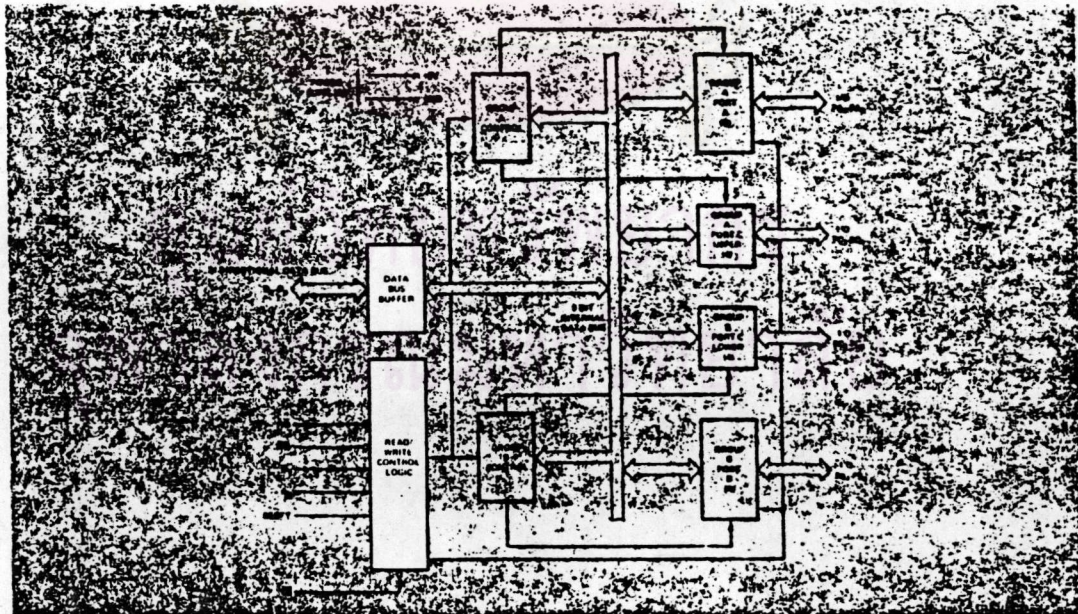
Write: A "low" on this input pin enables the 8080 CPU to write Data or Control words into the 8255.

(A₀ and A₁)

Port Select 0 and Port Select 1: These input signals, in conjunction with the RD and WR inputs, control the selection of one of the three ports or the Control Word Register. They are normally connected to the least significant bits of the Address Bus (A₀ and A₁).

8255 BASIC OPERATION

A ₁	A ₀	RD	WR	CS	INPUT OPERATION (READ)
0	0	0	1	0	PORT A - DATA BUS
0	1	0	1	0	PORT B - DATA BUS
1	0	0	1	0	PORT C - DATA BUS
					OUTPUT OPERATION (WRITE)
0	0	1	0	0	DATA BUS - PORT A
0	1	1	0	0	DATA BUS - PORT B
1	0	1	0	0	DATA BUS - PORT C
1	1	1	0	0	DATA BUS - CONTROL
					DISABLE FUNCTION
X	X	X	X	1	DATA BUS - 3-STATE
1	1	0	1	0	ILLEGAL CONDITION



8255 Block Diagram

SILICON GATE MOS 8255

(RESET)

Reset: A "high" on this input clears all internal registers including the Control Register and all ports (A, B, C) are set to the input mode.

Group A and Group B Controls

The functional configuration of each port is programmed by the systems software. In essence, the 8080 CPU "outputs" a control word to the 8255. The control word contains information such as "mode", "bit set", "bit reset" etc. that initializes the functional configuration of the 8255.

Each of the Control blocks (Group A and Group B) accepts "commands" from the Read/Write Control Logic, receives "control words" from the internal data bus and issues the proper commands to its associated ports.

Control Group A — Port A and Port C upper (C7-C4)

Control Group B — Port B and Port C lower (C3-C0)

The Control Word Register can Only be written into. No Read operation of the Control Word Register is allowed.

Ports A, B, and C

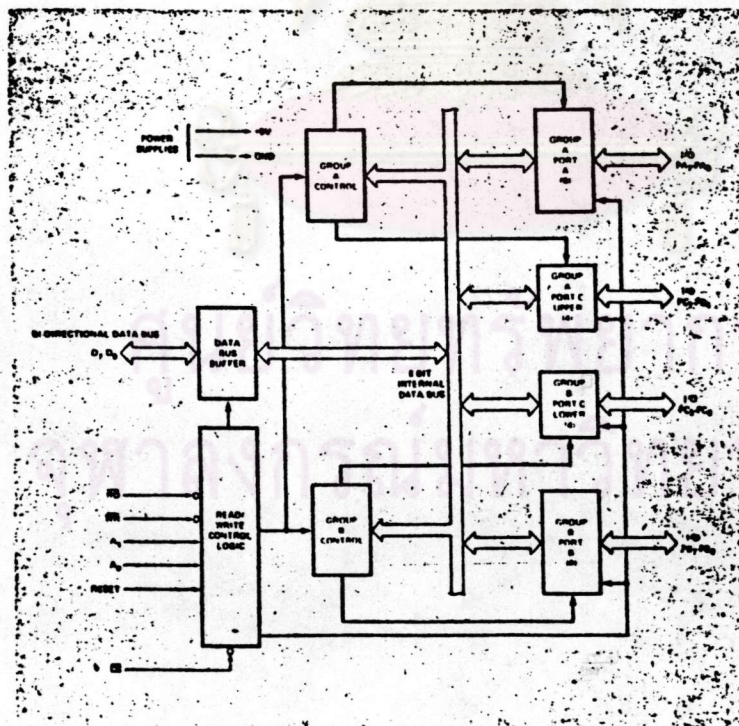
The 8255 contains three 8-bit ports (A, B, and C). All can be configured in a wide variety of functional characteristics by the system software but each has its own special features or "personality" to further enhance the power and flexibility of the 8255.

Port A: One 8-bit data output latch/buffer and one 8-bit data input latch.

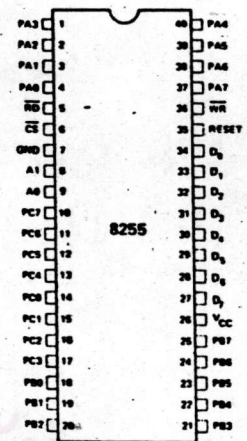
Port B: One 8-bit data input/output latch/buffer and one 8-bit data input buffer.

Port C: One 8-bit data output latch/buffer and one 8-bit data input buffer (no latch for input). This port can be divided into two 4-bit ports under the mode control. Each 4-bit port contains a 4-bit latch and it can be used for the control signal outputs and status signal inputs in conjunction with Ports A and B.

8255 BLOCK DIAGRAM



PIN CONFIGURATION



PIN NAMES

D ₇ -D ₀	DATA BUS (BI-DIRECTIONAL)
RESET	RESET INPUT
CS	CHIP SELECT
RD	READ INPUT
WR	WRITE INPUT
A0, A1	PORT ADDRESS
PA7-PA0	PORT A (8BIT)
PB7-PB0	PORT B (8BIT)
PC7-PC0	PORT C (8BIT)
V _{CC}	+5 VOLTS
GRD	0 VOLTS

SILICON GATE MOS 8255

8255 DETAILED OPERATIONAL DESCRIPTION

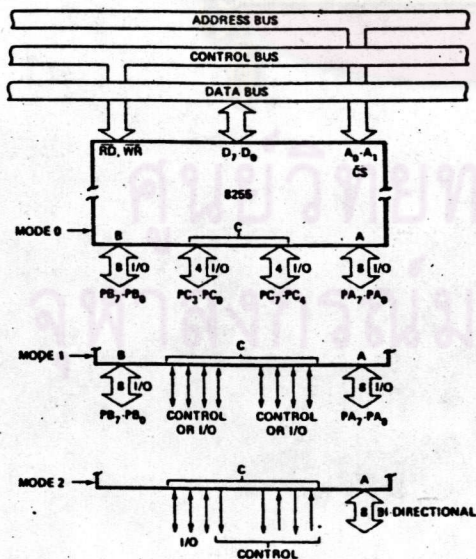
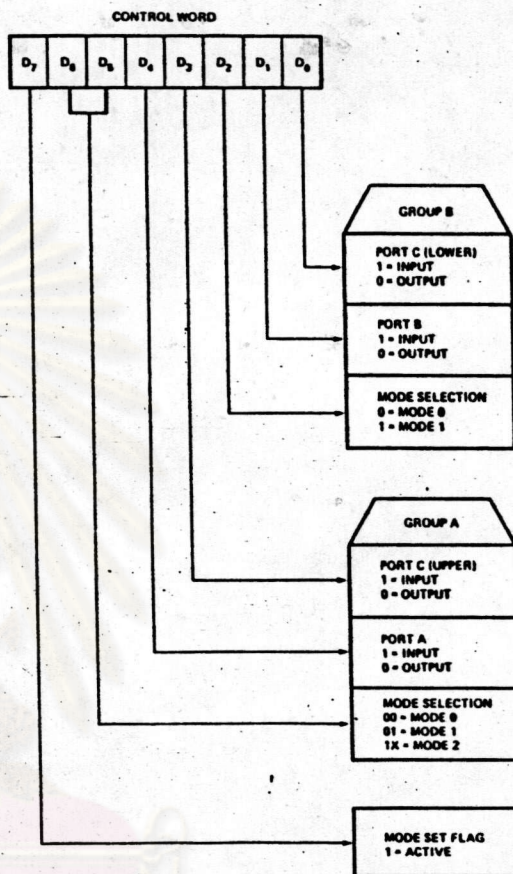
Mode Selection

There are three basic modes of operation that can be selected by the system software:

- Mode 0 - Basic Input/Output
- Mode 1 - Strobed Input/Output
- Mode 2 - Bi-Directional Bus

When the RESET input goes "high" all ports will be set to the Input mode (i.e., all 24 lines will be in the high impedance state). After the RESET is removed the 8255 can remain in the Input mode with no additional initialization required. During the execution of the system program any of the other modes may be selected using a single OUTPUT instruction. This allows a single 8255 to service a variety of peripheral devices with a simple software maintenance routine.

The modes for Port A and Port B can be separately defined, while Port C is divided into two portions as required by the Port A and Port B definitions. All of the output registers, including the status flip-flops, will be reset whenever the mode is changed. Modes may be combined so that their functional definition can be "tailored" to almost any I/O structure. For instance; Group B can be programmed in Mode 0 to monitor simple switch closings or display computational results, Group A could be programmed in Mode 1 to monitor a keyboard or tape reader on an interrupt-driven basis.



Basic Mode Definitions and Bus Interface

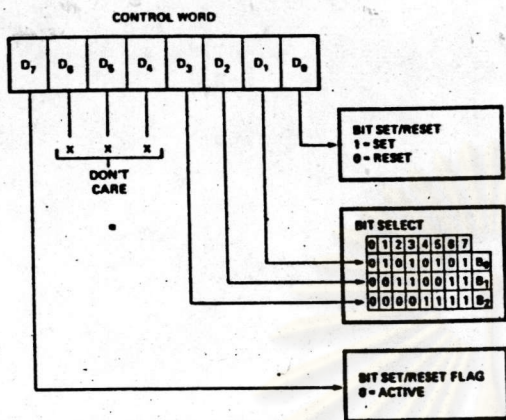
Mode Definition Format

The Mode definitions and possible Mode combinations may seem confusing at first but after a cursory review of the complete device operation a simple, logical I/O approach will surface. The design of the 8255 has taken into account things such as efficient PC board layout, control signal definition vs PC layout and complete functional flexibility to support almost any peripheral device with no external logic. Such design represents the maximum use of the available pins.

Single Bit Set/Reset Feature

Any of the eight bits of Port C can be Set or Reset using a single OUTPUT instruction. This feature reduces software requirements in Control-based applications.

SILICON GATE MOS 8255



When Port C is being used as status/control for Port A or B, these bits can be set or reset by using the Bit Set/Reset operation just as if they were data output ports.

Interrupt Control Functions

When the 8255 is programmed to operate in Mode 1 or Mode 2, control signals are provided that can be used as interrupt request inputs to the CPU. The interrupt request signals, generated from Port C, can be inhibited or enabled by setting or resetting the associated INTE flip-flop, using the Bit set/reset function of Port C.

This function allows the Programmer to disallow or allow a specific I/O device to interrupt the CPU without effecting any other device in the interrupt structure.

INTE flip-flop definition:

- (BIT-SET) – INTE is SET – Interrupt enable
- (BIT-RESET) – INTE is RESET – Interrupt disable

Note: All Mask flip-flops are automatically reset during mode selection and device Reset.

Bit Set/Reset Format

Operating Modes

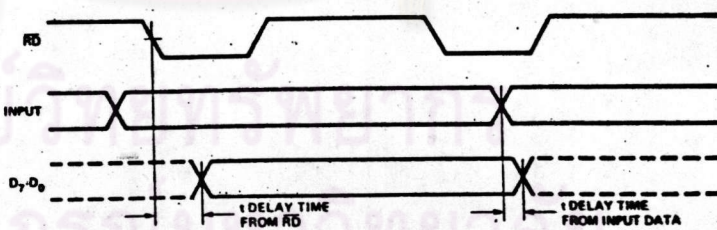
Mode 0 (Basic Input/Output)

This functional configuration provides simple Input and Output operations for each of the three ports. No "hand-shaking" is required, data is simply written to or read from a specified port.

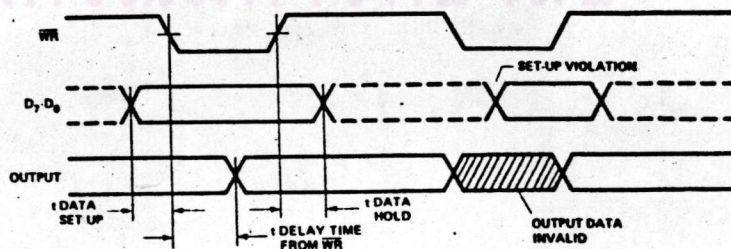
Mode 0 Basic Functional Definitions:

- Two 8-bit ports and two 4-bit ports.
- Any port can be input or output.
- Outputs are latched.
- Inputs are not latched.
- 16 different Input/Output configurations are possible in this Mode.

BASIC INPUT TIMING (D₇-D₀ FOLLOWS INPUT NO LATCHING)



BASIC OUTPUT TIMING (OUTPUTS LATCHED)



Mode 0 Timing

ภาคผนวก 6
ข้อมูลเกี่ยวกับไอซีเบอร์ 74138

54138/74138 3-Line-to-8-Line Decoder

	Schottky TTL				High-Speed TTL				Low-Power Schottky TTL				Standard TTL				Low-Power TTL				
	Device Type	Package			Device Type	Package			Device Type	Package			Device Type	Package			Device Type	Package			
		C	P	M	CF		C	P	M	CF		C	P	M	CF		C	P	M	CF	
T.I.	SN54S138	J	I		W						SN54LS138	J	I		W						
	SN74S138	J	I	N							SN74LS138	J	I	N							
FAIRCHILD	/FMSLS138	NC									/FMSLS138	NC									
	FC45138/FC35138	ND									FC45LS138/FC35LS138	ND									
MOTOROLA																					
N.S.C.																					
	DM74S138										DM74LS138										
PHILIPS																					
	N74S138										N74LS138										
SIGNETICS	S54S138	F	I	B	W																
	N74S138	F	I	B							N74LS138	F	I	B							
SIEMENS																					
FUJITSU																					
											74LS138										
HTACH																					
											HD74LS138										
MITSUBISHI																					
	M74S138										M74LS138										
NEC																					
											74LS138										
TOSHIBA																					

Electrical Characteristics SN54LS138/SN74LS138

absolute maximum ratings over operating free-air temperature range

Supply voltage, V _{CC}	TV	Operating free-air temperature range	SN54LS138	-55°C to 125°C
Input voltage	TV	temperature range	SN74LS138	0°C to 70°C
		Storage temperature range		-65°C to 150°C

recommended operating conditions

	SN54LS138			SN74LS138			UNIT
	MIN	NOM	MAX	MIN	NOM	MAX	
Supply voltage, V _{CC}	4.5	5	5.5	4.75	5	5.25	V
High-level output current, I _{OH}			400			400	mA
Low-level output current, I _{OL}			4			8	mA
Operating free-air temperature, T _A	-55		125	0		70	°C

electrical characteristics over recommended operating free-air temperature range

PARAMETER #	TEST CONDITIONS †	MIN	TYP ‡	MAX	UNIT	
V _{IH}	High-level input voltage		2		V	
V _{IL}	Low-level input voltage		0.8		V	
V _I	Input clamp voltage	V _{CC} = MIN, I _I = -18 mA		1.5	V	
V _{OH}	High-level output voltage	V _{CC} = MIN, V _{IH} = 2V, I _{OH} = 0.8V, I _{OH} = 400 mA	SN54LS138 2.5	3.4	V	
V _{OL}	Low-level output voltage	V _{CC} = MIN, V _{IL} = 2V, I _{OL} = 8 mA, I _{OL} = 8 mA	SN74LS138 0.35	0.5	V	
I _I	Input current at maximum input voltage	V _{CC} = MAX, V _I = 7V		0.1	mA	
I _{IH}	High-level input current	V _{CC} = MAX, V _I = 2.7V		20	µA	
I _{IL}	Low-level input current	V _{CC} = MAX, V _I = 0.4V		0.4	mA	
I _{OS}	Short-circuit output current †	V _{CC} = MAX	20	-100	mA	
I _{CC}	Supply current	V _{CC} = MAX, Outputs enabled and open	6.3	10	mA	
IP _{LH}	from Binary select	V _{CC} = 5V, T _A = 25°C, C _L = 15pF, R _L = 2kΩ	2	13	20	ns
IP _{HL}			3	27	41	ns
IP _{LH}			3	18	27	ns
IP _{HL}	to Any output		2	26	39	ns
IP _{LH}			2	12	18	ns
IP _{HL}	from Enable		2	21	32	ns
IP _{HL}			3	17	26	ns
IP _{LH}	to Any output		2	25	38	ns
IP _{HL}			3	25	38	ns

Pin Assignment (Top View)

Function Table

'S138' LS138

ENABLES		SELECT			OUTPUTS							
G1	G2	C	B	A	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	H	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	H	H	L	H	H	H	H	H	H
H	L	L	H	L	H	H	L	H	H	H	H	H
H	L	L	H	H	H	H	L	H	H	H	H	H
H	L	H	L	L	H	H	H	L	H	H	H	H
H	L	H	L	H	H	H	H	L	H	H	H	H
H	L	H	H	L	H	H	H	H	L	H	H	H
H	L	H	H	H	H	H	H	H	L	H	H	H

Functional Block Diagram

'S138' LS138 DECODER DEMULTIPLEXER

† For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions for the applicable device type.
 ‡ All typical values are at V_{CC} = 5V, T_A = 25°C.
 † Not more than one output should be shorted at a time, and duration of the short circuit test should not exceed ten seconds.
 IP_{LH} = propagation delay time, low-to-high-level output
 IP_{HL} = propagation delay time, high-to-low-level output

ภาคผนวก 7

ข้อมูลบางส่วนเกี่ยวกับไมโครโปรเซสเซอร์ Z-80

1. ซีพียู (หน่วยประมวลผลกลาง)

ใช้ซีพียูของ Zilog เบอร์ Z-80A โดยมีระบบสัญญาณนาฬิกา เท่ากับ 3.579 เมกกะเฮิร์ตซ์

2. รอม (หน่วยความจำอ่านอย่างเดียว)

สามารถใช้ได้ทั้งรอมเบอร์ 2732 และเบอร์ 2764 โดยมี แอดเดรสดังนี้

- กรณีใช้กับรอมเบอร์ 2732 เป็นตัวเผ่าตรวจ (monitor) (มีขนาด 4 กิโลไบต์) มีแอดเดรสอยู่ที่ 0000 - 0FFFH
- กรณีใช้กับรอมเบอร์ 2764 เป็นตัวเผ่าตรวจ (monitor) (มีขนาด 8 กิโลไบต์) มีแอดเดรสอยู่ที่ 0000 - 1FFFH

3. แรม (หน่วยความจำเข้าถึงแบบสุ่ม)

ใช้แรมแบบสถิตเบอร์ 6264 มีขนาด 8 กิโลไบต์ โดยมีหน่วย ความจำอยู่ที่ 4000 - 5FFFH

4. ส่วนขยายหน่วยความจำ

ส่วนขยายหน่วยความจำ 8 กิโลไบต์นี้ สามารถเป็นได้ทั้งรอม และแรม กรณีที่เป็นรอมจะใช้ได้ทั้งเบอร์ 2732 และเบอร์ 2764

ถ้าใช้ 2732 ซึ่งมีขนาด 4 กิโลไบต์ มีแอดเดรสอยู่ที่ 2000 - 2FFFH

ถ้าใช้ 2764 ซึ่งมีขนาด 8 กิโลไบต์ มีแอดเดรสอยู่ที่ 2000 - 3FFFH

กรณีที่ เป็นแรม (ให้ลัดวงจรภายในเข้าด้วยกัน) ใช้ 6264
 ซึ่งมีขนาด 8 กิโลไบต์ มีแอดเดรสอยู่ที่ 2000 - 3FFFH

5. อุปกรณ์ติดต่อภายนอก

8255	มีแอดเดรสอยู่ที่	00 - 03H
Z-80 PIO	มีแอดเดรสอยู่ที่	40 - 43H
Z-80 CTC	มีแอดเดรสอยู่ที่	80 - 83H

6. ภาคแสดงผล

ใช้แอลอีดี (ไดโอดเปล่งแสง) แบบ 7 เซ็กเมนต์ ขนาด
 ความสูง 0.5 นิ้ว จำนวน 6 หลัก

7. แป้นพิมพ์ ใช้แบบ 24 แป้นกด

8. แหล่งกำเนิดเสียง ลำโพงของ Sony ขนาด 1 นิ้ว

9. ลักษณะการเชื่อมโยงเครื่องเล่นเทป 83 บิตต่อวินาที

10. อัตราของสัญญาณนาฬิกาในระบบ 3.579 เมกกะเฮิร์ตซ์

11. ขั้วต่อ

- 40 ขา มาจากซีพียูโดยตรง

- 10 ขา มาจากวงจรถอดรหัสของหน่วยความจำ และ

ด้านนอกของ Z-80 CTC

- 28 ขา มาจาก Z-80 PIO และ Z-80 CTC
- ช่องเสียบ 50 ขา โดย 40 ขา มาจากซีพียูโดยตรง,
5 ขา มาจากวงจรถอดรหัสของหน่วยความจำ และ
5 ขา มาจากวงจรถอดรหัสของอุปกรณ์ติดต่อภายนอก

แมปของหน่วยความจำ

แอดเดรสเริ่มต้น	อุปกรณ์ที่ใช้
0000H - 0FFFH	โปรแกรมมอนิเตอร์ 4 กิโลไบต์ (2732)
1000H - 1FFFH	โปรแกรมมอนิเตอร์ส่วนขยาย 8 กิโลไบต์ (2764)
2000H - 3FFFH	ส่วนขยายหน่วยความจำ 8 กิโลไบต์ 2732 มีแอดเดรสอยู่ที่ 2000H - 2FFFH 2764, 6264 มีแอดเดรสอยู่ที่ 2000H - 3FFFH
4000H - 5FFFH	หน่วยความจำ 8 กิโลไบต์ (6264)
6000H - FFFFH	สำหรับผู้ขยายหน่วยความจำ

แมปของด้านเข้าและด้านออก

หมายเลขของทางเข้าออก	ชื่อของทางเข้าออก	อุปกรณ์
00	PORT A	
01	PORT B	8255
02	PORT C	
03	CONTROL	
40	PIO DA	
41	PIO DB	Z-80 PIO
42	PIO CA	
43	PIO CB	
80	CTC 00	
81	CTC 01	Z-80 CTC
82	CTC 02	
83	CTC 03	

ศูนย์วิทยทรัพยากร
จุฬาลงกรณ์มหาวิทยาลัย

หน่วยความจำที่ใช้งานและหน่วยความจำสแตก

4000H

ส่วนของโปรแกรมใช้งาน

บริเวณสแตกของผู้ใช้ที่กำหนดขึ้นเอง

5F80H

บริเวณสแตกของโปรแกรมมอไนเตอร์

5F96H

บัฟเฟอร์

5FFFH

ศูนย์วิทยพัทยากร
จุฬาลงกรณ์มหาวิทยาลัย

Z80[®]-CPU Z80A-CPU

Product Specification MARCH 1978

The Zilog Z80 product line is a complete set of micro-computer components, development systems and support software. The Z80 microcomputer component set includes all of the circuits necessary to build high-performance microcomputer systems with virtually no other logic and a minimum number of low cost standard memory elements.

The Z80 and Z80A CPU's are third generation single chip microprocessors with unrivaled computational power. This increased computational power results in higher system through-put and more efficient memory utilization when compared to second generation microprocessors. In addition, the Z80 and Z80A CPU's are very easy to implement into a system because of their single voltage requirement plus all output signals are fully decoded and timed to control standard memory or peripheral circuits. The circuit is implemented using an N-channel, ion implanted, silicon gate MOS process.

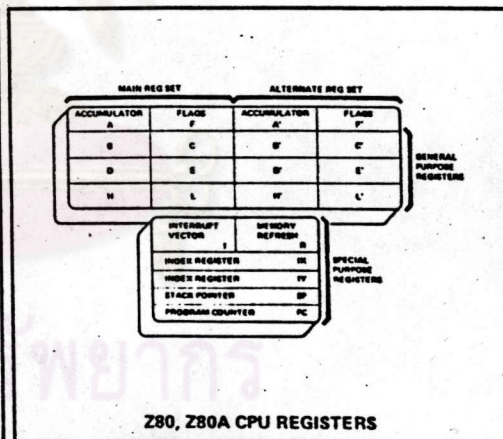
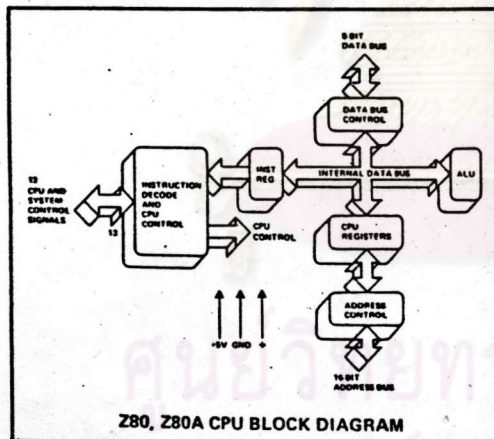
Figure 1 is a block diagram of the CPU, Figure 2 details the internal register configuration which contains 208 bits of Read/Write memory that are accessible to the programmer. The registers include two sets of six general purpose registers that may be used individually as 8-bit registers or as 16-bit register pairs. There are also two sets of accumulator and flag registers. The programmer has access to either set of main or alternate registers through a group of exchange instructions. This alternate set allows foreground/background mode of operation or may be reserved for very fast Interrupt response. Each CPU also contains a 16-bit stack pointer which permits simple implementation of

multiple level interrupts, unlimited subroutine nesting and simplification of many types of data handling.

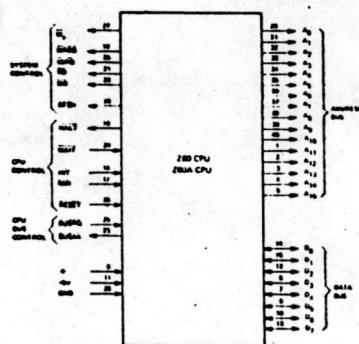
The two 16-bit index registers allow tabular data manipulation and easy implementation of relocatable code. The Refresh register provides for automatic, totally transparent refresh of external dynamic memories. The I register is used in a powerful interrupt response mode to form the upper 8 bits of a pointer to an interrupt service address table, while the interrupting device supplies the lower 8 bits of the pointer. An indirect call is then made to this service address.

FEATURES

- Single chip, N-channel Silicon Gate CPU.
- 158 instructions—includes all 78 of the 8080A instructions with total software compatibility. New instructions include 4-, 8- and 16-bit operations with more useful addressing modes such as indexed, bit and relative.
- 17 internal registers.
- Three modes of fast interrupt response plus a non-maskable interrupt.
- Directly interfaces standard speed static or dynamic memories with virtually no external logic.
- 1.0 μ s instruction execution speed.
- Single 5 VDC supply and single-phase 5 volt Clock.
- Out-performs any other single chip microcomputer in 4-, 8-, or 16-bit applications.
- All pins TTL Compatible
- Built-in dynamic RAM refresh circuitry.



Z80, Z80A-CPU Pin Description



A₀-A₁₅ (Address Bus)
Tri-state output, active high. A₀-A₁₅ constitute a 16-bit address bus. The address bus provides the address for memory (up to 64K bytes) data exchanges and for I/O device data exchanges.

D₀-D₇ (Data Bus)
Tri-state input/output, active high. D₀-D₇ constitute an 8-bit bidirectional data bus. The data bus is used for data exchanges with memory and I/O devices.

M₁ (Machine Cycle one)
Output, active low. \overline{M}_1 indicates that the current machine cycle is the OP code fetch cycle of an instruction execution.

MREQ (Memory Request)
Tri-state output, active low. The memory request signal indicates that the address bus holds a valid address for a memory read or memory write operation.

$\overline{\text{IORQ}}$
(Input/
Output
Request)

Tri-state output, active low. The $\overline{\text{IORQ}}$ signal indicates that the lower half of the address bus holds a valid I/O address for a I/O read or write operation. An $\overline{\text{IORQ}}$ signal is also generated when an interrupt is being acknowledged to indicate that an interrupt response vector can be placed on the data bus.

 $\overline{\text{RD}}$
(Memory
Read)

Tri-state output, active low. $\overline{\text{RD}}$ indicates that the CPU wants to read data from memory or an I/O device. The addressed I/O device or memory should use this signal to gate data onto the CPU data bus.

 $\overline{\text{WR}}$
(Memory
Write)

Tri-state output, active low. $\overline{\text{WR}}$ indicates that the CPU data bus holds valid data to be stored in the addressed memory or I/O device.

 $\overline{\text{RFSH}}$
(Refresh)

Output, active low. $\overline{\text{RFSH}}$ indicates that the lower 7 bits of the address bus contain a refresh address for dynamic memories and the current $\overline{\text{MREQ}}$ signal should be used to do a refresh read to all dynamic memories.

 $\overline{\text{HALT}}$
(Halt state)

Output, active low. $\overline{\text{HALT}}$ indicates that the CPU has executed a HALT software instruction and is awaiting either a non-maskable or a maskable interrupt (with the mask enabled) before operation can resume. While halted, the CPU executes NOP's to maintain memory refresh activity.

 $\overline{\text{WAIT}}$
(Wait)

Input, active low. $\overline{\text{WAIT}}$ indicates to the Z-80 CPU that the addressed memory or I/O devices are not ready for a data transfer. The CPU continues to enter wait states for as long as this signal is active.

 $\overline{\text{INT}}$
(Interrupt
Request)

Input, active low. The Interrupt Request signal is generated by I/O devices. A request will be honored at the end of the current instruction if the internal software controlled interrupt enable flip-flop (IFF) is enabled.

 $\overline{\text{NMI}}$
(Non
Maskable
Interrupt)

Input, active low. The non-maskable interrupt request line has a higher priority than $\overline{\text{INT}}$ and is always recognized at the end of the current instruction, independent of the status of the interrupt enable flip-flop. $\overline{\text{NMI}}$ automatically forces the Z-80 CPU to restart to location 0066H.

 $\overline{\text{RESET}}$

Input, active low. $\overline{\text{RESET}}$ initializes the CPU as follows: reset interrupt enable flip-flop, clear PC and registers I and R and set interrupt to 8080A mode. During reset time, the address and data bus go to a high impedance state and all control output signals go to the inactive state.

 $\overline{\text{BUSRQ}}$
(Bus
Request)

Input, active low. The bus request signal has a higher priority than $\overline{\text{NMI}}$ and is always recognized at the end of the current machine cycle and is used to request the CPU address bus, data bus and tri-state output control signals to go to a high impedance state so that other devices can control these buses.

 $\overline{\text{BUSAK}}$
(Bus
Acknowledge)

Output, active low. Bus acknowledge is used to indicate to the requesting device that the CPU address bus, data bus and tri-state control bus signals have been set to their high impedance state and the external device can now control these signals.

Absolute Maximum Ratings

Temperature Under Bias
Storage Temperature
Voltage On Any Pin
with Respect to Ground
Power Dissipation

Specified operating range:
-55°C to +150°C
-0.3V to +7V
1.5W

*Comment

Stresses above those listed under "Absolute Maximum Rating" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note: For Z80-CPU all AC and DC characteristics remain the same for the military grade parts except I_{CC} .

$$I_{CC} = 200 \text{ mA}$$

Z80-CPU D.C. Characteristics

$T_A = 0^\circ\text{C}$ to 70°C , $V_{CC} = 5V \pm 5\%$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
V_{ILC}	Clock Input Low Voltage	-0.3		0.45	V	
V_{IHC}	Clock Input High Voltage	$V_{CC} - 0.6$		$V_{CC} + 0.3$	V	
V_{IL}	Input Low Voltage	-0.3		0.8	V	
V_{IH}	Input High Voltage	2.0		V_{CC}	V	
V_{OL}	Output Low Voltage			0.4	V	$I_{OL} = 1.2 \text{ mA}$
V_{OH}	Output High Voltage	2.4			V	$I_{OH} = -250 \mu\text{A}$
I_{CC}	Power Supply Current			150	mA	
I_{LI}	Input Leakage Current			10	μA	$V_{IN} = 0$ to V_{CC}
I_{LOH}	Tri-State Output Leakage Current in Float			10	μA	$V_{OUT} = 2.4$ to V_{CC}
I_{LOL}	Tri-State Output Leakage Current in Float			-10	μA	$V_{OUT} = 0.4V$
I_{LD}	Data Bus Leakage Current in Input Mode			110	μA	$0 < V_{IN} < V_{CC}$

Capacitance

$T_A = 25^\circ\text{C}$, $f = 1 \text{ MHz}$,
unmeasured pins returned to ground

Symbol	Parameter	Max.	Unit
C_ϕ	Clock Capacitance	35	pF
C_{IN}	Input Capacitance	5	pF
C_{OUT}	Output Capacitance	10	pF

Z80-CPU Ordering Information

C - Ceramic
P - Plastic
S - Standard 5V $\pm 5\%$ 0° to 70°C
E - Extended 5V $\pm 5\%$ -40° to 85°C
M - Military 5V $\pm 10\%$ -55° to 125°C



A.C. Characteristics

Z80-CPU

T_A = 0°C to 70°C, V_{CC} = +5V ± 5%, Unless Otherwise Noted.

Signal	Symbol	Parameter	Min	Max	Unit	Test Condition
φ	t _{CL} (PH)	Clock Period	4	11.25	μsec	
	t _{PH} (PH)	Clock Pulse Width, Clock High	180	18	nsec	
	t _{PL} (PH)	Clock Pulse Width, Clock Low	180	300	nsec	
	t _{CL}	Clock Rise and Fall Time		40	nsec	
A ₀₋₁₅	t _D (AD)	Address Output Delay		12.5	nsec	C _L = 50pF
	t _F (AD)	Delay to Float		110	nsec	
	t _{dc}	Address Stable Prior to MREQ (Memory Cycle)	111		nsec	
	t _{dc}	Address Stable Prior to IORQ RD or WR (I/O Cycle)	121		nsec	
	t _{dc}	Address Stable from RD, WR, IORQ or MREQ	131		nsec	
	t _{dc}	Address Stable from RD or WR During Float	141		nsec	
D ₀₋₇	t _D (D)	Data Output Delay		230	nsec	C _L = 50pF
	t _F (D)	Delay to Float During Write Cycle		90	nsec	
	t _{su} (D)	Data Setup Time to Rising Edge of Clock During M1 Cycle	90		nsec	
	t _{su} (D)	Data Setup Time to Falling Edge of Clock During M2 to M5	50		nsec	
	t _{dc}	Data Stable Prior to WR (Memory Cycle)	151		nsec	
	t _{dc}	Data Stable Prior to WR (I/O Cycle)	161		nsec	
	t _{dc}	Data Stable from WR	171		nsec	
t _H	Any Hold Time for Setup Time	0		nsec		
MREQ	t _D (MR)	MREQ Delay From Falling Edge of Clock, MREQ Low		100	nsec	C _L = 50pF
	t _D (MR)	MREQ Delay From Rising Edge of Clock, MREQ High		100	nsec	
	t _D (MR)	MREQ Delay From Falling Edge of Clock, MREQ High		100	nsec	
	t _w (MRL)	Pulse Width, MREQ Low	181		nsec	
	t _w (MRH)	Pulse Width, MREQ High	191		nsec	
IORQ	t _D (IR)	IORQ Delay From Rising Edge of Clock, IORQ Low		90	nsec	C _L = 50pF
	t _D (IR)	IORQ Delay From Falling Edge of Clock, IORQ Low		110	nsec	
	t _D (IR)	IORQ Delay From Rising Edge of Clock, IORQ High		100	nsec	
	t _D (IR)	IORQ Delay From Falling Edge of Clock, IORQ High		110	nsec	
RD	t _D (RD)	RD Delay From Rising Edge of Clock, RD Low		100	nsec	C _L = 50pF
	t _D (RD)	RD Delay From Falling Edge of Clock, RD Low		130	nsec	
	t _D (RD)	RD Delay From Rising Edge of Clock, RD High		100	nsec	
	t _D (RD)	RD Delay From Falling Edge of Clock, RD High		110	nsec	
WR	t _D (WR)	WR Delay From Rising Edge of Clock, WR Low		80	nsec	C _L = 50pF
	t _D (WR)	WR Delay From Falling Edge of Clock, WR Low		90	nsec	
	t _D (WR)	WR Delay From Falling Edge of Clock, WR High		100	nsec	
	t _w (WRL)	Pulse Width, WR Low	1101		nsec	
M1	t _D (M1)	M1 Delay From Rising Edge of Clock, M1 Low		130	nsec	C _L = 50pF
	t _D (M1)	M1 Delay From Rising Edge of Clock, M1 High		130	nsec	
RFSH	t _D (RF)	RFSH Delay From Rising Edge of Clock, RFSH Low		160	nsec	C _L = 50pF
	t _D (RF)	RFSH Delay From Rising Edge of Clock, RFSH High		150	nsec	
WAIT	t _s (WT)	WAIT Setup Time to Falling Edge of Clock	70		nsec	
HALT	t _D (HT)	HALT Delay Time From Falling Edge of Clock		300	nsec	C _L = 50pF
INT	t _s (IT)	INT Setup Time to Rising Edge of Clock	80		nsec	
NMI	t _w (NML)	Pulse Width, NMI Low	80		nsec	
BUSRQ	t _s (BR)	BUSRQ Setup Time to Rising Edge of Clock	80		nsec	
BUSAK	t _D (BA)	BUSAK Delay From Rising Edge of Clock, BUSAK Low		120	nsec	C _L = 50pF
	t _D (BA)	BUSAK Delay From Falling Edge of Clock, BUSAK High		110	nsec	
RESET	t _s (RS)	RESET Setup Time to Rising Edge of Clock	90		nsec	
	t _F (C)	Delay to Float (MREQ, IORQ, RD and WR)		100	nsec	
	t _{su}	M1 Stable Prior to IORQ (Interrupt Ack)	1111		nsec	

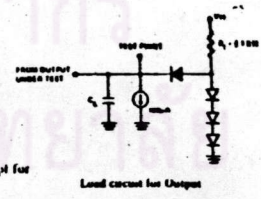
[12] $t_{CL} = t_{su(AD)} + t_{su(D)} + t_{su}$
 [13] $t_{dc} = t_{su(AD)} + t_{su} - 75$
 [14] $t_{dc} = t_{su(D)} + t_{su} - 40$
 [15] $t_{dc} = t_{su} - 210$
 [16] $t_{dc} = t_{su(D)} + t_{su} - 210$
 [17] $t_{dc} = t_{su(D)} + t_{su} - 80$

[18] $t_w(MRL) = t_{su} - 40$
 [19] $t_w(MRH) = t_{su(AD)} + t_{su} - 30$
 [10] $t_w(WRL) = t_{su} - 40$

[11] $t_{su} = t_{su(AD)} + t_{su} + t_{su}$

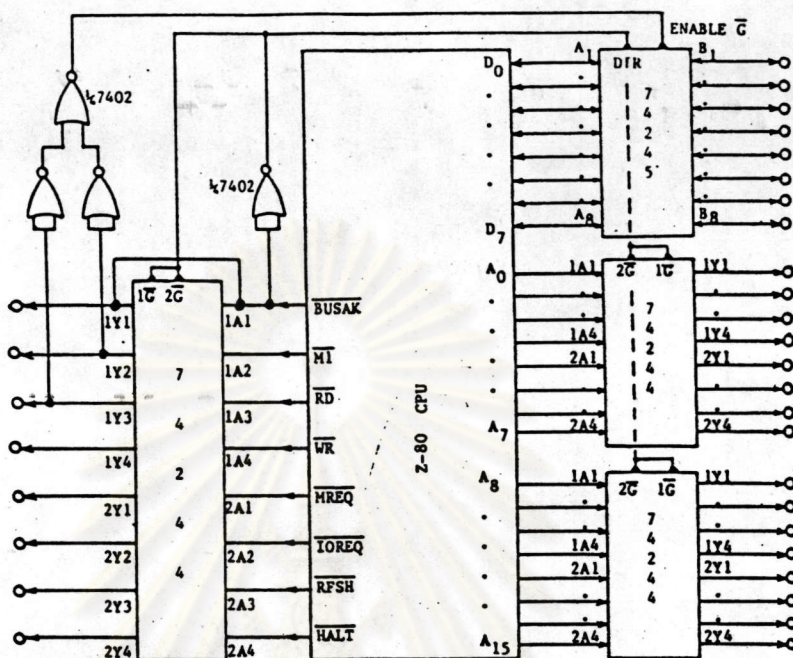
NOTES

- A. Data should be enabled onto the CPU data bus when RD is active. During interrupt acknowledge data should be enabled when M1 and IORQ are both active.
- B. All control signals are internally synchronized, so they may be totally asynchronous with respect to the clock.
- C. The RESET signal must be active for a maximum of 3 clock cycles.
- D. Output Delay vs. Loaded Capacitance
 $T_A = 0^\circ C \quad V_{CC} = +5V \pm 5\%$
 Add 10nsec delay for each 50pF increase in load up to a maximum of 200pF for the data bus & 100pF for address & control lines.
- E. Although stated by design, testing guarantees $t_{su(AD)}$ of 200nsec maximum.



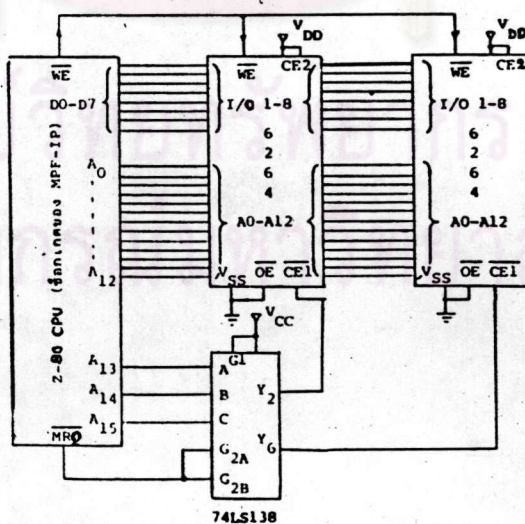
การต่อวงจรรับบัลและหน่วยความจำเพิ่มเติมให้แก่ไมโครโปรเซสเซอร์ Z-80

รูปที่ ๗7-1 แสดงการต่อวงจรรับ(driver) ให้แก่บัลต่าง ๆ ของไมโครโปรเซสเซอร์ Z-80 องค์ประกอบที่สำคัญในวงจรนี้ ก็คือไอซีเบอร์ 74244 กับ 74245 ซึ่งเป็นตัวขับสาย(line driver) และไอซีเบอร์ 7402 ซึ่งเป็นเกตแบบนอร์(NOR gate)



รูปที่ ๗7-1 วงจรรับบัลที่ต่อเพิ่มให้แก่ไมโครโปรเซสเซอร์ Z-80

รูปที่ ๗7-2 แสดงการต่อหน่วยความจำเพิ่มเติมให้แก่ ไมโครโปรเซสเซอร์ Z-80 ไอซีหน่วยความจำที่ใช้ก็คือแรม(RAM)เบอร์ 6264 จำนวน 2 ตัว แต่ละตัวมีขนาดความจุ 8 กิโลไบต์ องค์ประกอบที่ใช้ควบคุมการเลือกไอซีเบอร์ 6264 แต่ละตัว ก็คือไอซีเบอร์ 74LS138 ซึ่งทำหน้าที่เหมือนกับไอซีเบอร์ 74138 ในภาคผนวก 6 นั้นเอง



รูปที่ ๗7-2 วงจรหน่วยความจำเพิ่มเติมสำหรับไมโครโปรเซสเซอร์ Z-80

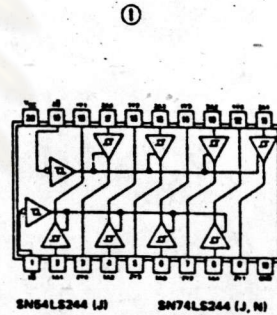
54244/74244 Octal Buffers/Line Drivers/Line Receivers

	Schttky TTL				High-Speed TTL				Low-Power Schottky TTL				Standard TTL				Low-Power TTL					
	Device Type		Package		Device Type		Package		Device Type		Package		Device Type		Package		Device Type		Package			
	C	P	M	C	P	M	C	P	M	C	P	M	C	P	M	C	P	M	C	P	M	C
T. I.																						
FAIRCHILD																						
MOTOROLA																						
N. S. C.																						
PHILIPS																						
SIGNETICS																						
SIEMENS																						
FUJITSU																						
HITACHI																						
MITSUBISHI																						
NEC																						
TOSHIBA																						

Electrical Characteristics SN54LS244/SN74LS244					
absolute maximum ratings over operating free-air temperature range					
Supply voltage, VCC	TV	Operating free-air temperature range	SN54LS	55°C to 125°C	
Input voltage	5.5V	temperature range	SN74LS	0°C to 70°C	
Intermittent voltage	5.5V	Storage temperature range		65°C to 150°C	
recommended operating conditions					
	LS54LS244		SN74LS244		
	MIN	NOM	MAX	UNIT	
Supply voltage, VCC	4.5	5	5.5	V	
High-level output current, IOH			12	mA	
Low-level output current, IOL			24	mA	
Operating free-air temperature, TA	55		125	°C	
electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)					
PARAMETER	TEST CONDITIONS †	SN74LS			UNIT
		MIN	TYP ‡	MAX	
V _{IH} High-level input voltage			2		V
V _{IL} Low-level input voltage				0.8	V
V _{IK} Input clamp voltage	VCC - MIN, I _I = 18mA			1.5	V
Hysteresis (V _{T+} - V _{T-})					
	VCC - MIN		0.2	0.4	V
V _{OH} High-level output voltage	VCC - MIN, V _{IH} = 2V, V _{IL} = V _{ILmax} , I _{OH} = -3mA		2.4	3.4	V
	VCC = MIN, V _{IH} = 2V, V _{IL} = 0.5V, I _{OH} = MAX		2		V
V _{OL} Low-level output voltage	VCC = MIN, V _{IH} = 2V, V _{IL} = V _{ILmax}	I _{OL} = 12mA		0.4	V
		I _{OL} = 24mA		0.5	V
IOZH Off-state output current, high-level voltage applied	VCC = MAX, V _O = 2.7V, V _{IH} = 2V			20	µA
IOZL Off-state output current, low-level voltage applied	VCC = MAX, V _O = 0.4V, V _{IL} = V _{ILmax}			-20	µA
I _I Input current at maximum input voltage	VCC = MAX, V _I = 7V			0.1	mA
I _{IH} High-level input current, any input	VCC = MAX, V _I = 2.7V			20	µA
I _{IL} Low-level input current	VCC = MAX, V _I = 0.4V			0.2	mA
I _{OS} Short-circuit output current †	VCC = MAX		40	-225	mA
I _{CC} Supply current	Outputs high	VCC = MAX	AR	13	23
	Outputs low		LS244	27	46
	At outputs disabled		LS244	32	54
switching characteristics, VCC 5V, TA 25°C					
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} Propagation delay time, low-to-high-level output			9	14	ns
t _{PHL} Propagation delay time, high-to-low-level output	C _L = 45pF, R _L = 667Ω, See Note 2		12	18	ns
t _{DZL} Output enable time to low level			20	30	ns
t _{DZH} Output enable time to high level			15	23	ns
t _{PLZ} Output disable time from low level	C _L = 50pF, R _L = 667Ω, See Note 2		15	25	ns
t _{PHZ} Output disable time from high level			10	18	ns

† For conditions shown as MIN or MAX use the appropriate value specified under recommended operating conditions
 ‡ All typical values are at VCC 5V, TA 25°C
 § Not more than one output should be shorted at a time and duration of the short-circuit should not exceed the allowed
 NOTE 2 : Load circuit and voltage wave forms are shown on page 3-11

Pin Assignment (Top View)



SN54LS244 (J) SN74LS244 (J, N)

พยากกร
 วิทยาลัย

54245/74245 Octal Bus Transceivers with 3-state Outputs

	Schottky TTL				High-Speed TTL				Low-Power Schottky TTL				Standard TTL				Low-Power TTL				
	Device Type		Package		Device Type		Package		Device Type		Package		Device Type		Package		Device Type		Package		
	C	P	MCF		C	P	MCF		C	P	MCF		C	P	MCF		C	P	MCF		
T. I.									SN54LS245	J	I	W	W								
FAIRCHILD									SN74LS245	J	I	W	W								
MOTOROLA																					
N. S. C.																					
PHILIPS																					
SIGNETICS																					
SIEMENS																					
FUJITSU																					
HITACHI																					
MITSUBISHI																					
NEC																					
TOSHIBA																					

Electrical Characteristics SN54LS245/SN74LS245

absolute maximum ratings over operating free-air temperature range

Supply voltage, VCC	7V	Operating free-air temperature range	SN54LS	55°C to 125°C
Input voltage	7V	Storage temperature range	SN74LS	0°C to 70°C
		Storage temperature range		65°C to 150°C

recommended operating conditions

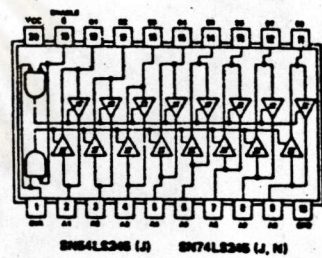
	SN54LS245			SN74LS245			UNIT
	MIN	NOM	MAX	MIN	NOM	MAX	
Supply voltage, VCC	4.5	5	5.5	4.75	5	5.25	V
High-level output current, IOH			12			15	mA
Low-level output current, IOL			12			24	mA
Operating free air temperature, TA	55		125	0		70	°C

electrical characteristics over recommended operating free-air temperature range

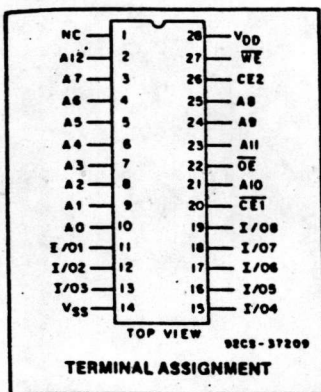
PARAMETER	TEST CONDITIONS†	SN74LS245		UNIT
		MIN	TYP‡	
VIH High-level input voltage			2	V
VIL Low-level input voltage			0.8	V
VIK Input clamp voltage	VCC = MIN, Ii = -18mA		-1.5	V
	Hysteresis (VT+ - VT-) A or B input		0.2 0.4	V
VOH High-level output voltage	VCC = MIN, VIH = 2V, VIL = VILmax	IOH = 3mA	2.4 3.4	V
		IOH = MAX	2	
VOL Low-level output voltage	VCC = MIN, VIH = 2V, VIL = VILmax	IOL = 12mA	0.4	V
		IOL = 24mA	0.5	
IOZH Off-state output current, high-level voltage applied	VCC = MAX, 0 at 2V	VO = 2.7 V	10	µA
IOZL Off-state output current, low-level voltage applied		VO = 0.4V	200	
Ii Input current at maximum input voltage	A or B DIR or 0	VCC = MAX, Vi = 5.5V	0.1	mA
		Vi = 7V	0.1	
IiH High-level input current	VCC = MAX, VIH = 2.7V		20	µA
IiL Low-level input current	VCC = MAX, VIL = 0.4V		-0.2	mA
IOS Short-circuit output current	VCC = MAX		40 225	mA
Icc Supply current	Total outputs high	VCC = MAX, Outputs open	48 70	mA
	Total outputs low		62 90	
	Outputs at Hi-Z		64 95	

switching characteristics, VCC 5V, TA 25°C

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
tPLH Propagation delay time, low-to-high-level output			8 12		ns
tPHL Propagation delay time, high-to-low-level output	CL = 45pF, RL = 647Ω, See Note 2		8 12		ns
tPZL Output enable time to low level			27 40		ns
tPZH Output enable time to high level			25 40		ns
tPLZ Output disable time from low level	CL = 5pF, RL = 647Ω, See Note 2		15 25		ns
tPHZ Output disable time from high level			15 25		ns



† For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
 ‡ All typical values are at VCC = 5V, TA = 25°C.
 § Not more than one output should be shorted at a time, and duration of the short-circuit should not exceed one second.



CMOS 8192-Word by 8-Bit LSI Static RAM

Features:

- Fully static operation
- Single power supply: 4.5 V to 5.5 V
- All inputs and outputs directly TTL compatible
- 3-state outputs
- Industry standard 28-pin configuration
- Input address buffers gated off with chip disable
- Fast access time: $t_{AA}=150\text{ ns}/120\text{ ns}$ (CDM6264-3/CDM6264-4)
- Low standby and operating power: $I_{OBS1}=2\ \mu\text{A}$ typical, $I_{OPER3}=40\text{ mA}$ maximum
- Data retention voltage: 2 V min.
- Operating temperature range (max. rating): 0° to 70° C

The RCA-CDM6264 is a 8192-word by 8-bit static random-access memory. It is designed for use in memory systems where high-speed, low power and simplicity in use are desirable. This device has common data input and data output and utilizes a single power supply of 4.5 V to 5.5 V. Either chip enable ($\overline{\text{CE1}}$ or $\overline{\text{CE2}}$), when not valid, will gate off the address and output buffers and power down the chip to

minimum standby power with inputs toggling. The output enable ($\overline{\text{OE}}$) controls the output buffers to eliminate bus contention.

The CDM6264 is supplied in 28-lead, hermetic, dual-in-line side-brazed ceramic (D suffix) and in 28-lead dual-in-line plastic (E suffix) packages.

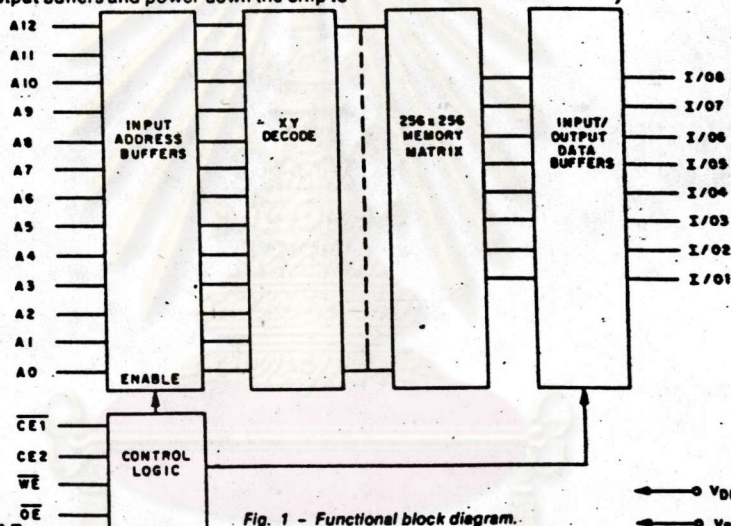


Fig. 1 - Functional block diagram.

TRUTH TABLE

$\overline{\text{CE1}}$	$\overline{\text{CE2}}$	$\overline{\text{OE}}$	$\overline{\text{WE}}$	A0 TO A12	MODE	DATA I/O	DEVICE CURRENT
H	X	X	X	X	NOT SELECTED	HIGH Z	STANDBY
X	L	X	X	X	NOT SELECTED	HIGH Z	STANDBY
L	H	L	H	STABLE	READ	DATA OUT	ACTIVE
L	H	X	L	STABLE	WRITE	DATA IN	ACTIVE
L	H	H	H	STABLE	OUTPUT DISABLE	HIGH Z	ACTIVE

L = LOW H = HIGH X = H OR L

MAXIMUM RATINGS, Absolute-Maximum Values:

- DC SUPPLY-VOLTAGE RANGE, (V_{DD}):
(Voltage referenced to V_{SS} terminal) -0.3 to +7 V
- INPUT VOLTAGE RANGE, ALL INPUTS -0.3 to +7 V
- POWER DISSIPATION PER PACKAGE (P_D):
For $T_A = 0^\circ$ to $+60^\circ\text{C}$ (PACKAGE TYPE E) 500 mW
For $T_A = +60^\circ$ to $+70^\circ\text{C}$ (PACKAGE TYPE E) Derate Linearly at 8 mW/ $^\circ\text{C}$ to 420 mW
For $T_A = 0^\circ$ to $+70^\circ\text{C}$ (PACKAGE TYPE D) 500 mW
- DEVICE DISSIPATION PER OUTPUT TRANSISTOR
For $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE}$ 100 mW
- OPERATING-TEMPERATURE RANGE (T_A):
PACKAGE TYPE D 0 to $+70^\circ\text{C}$
PACKAGE TYPE E 0 to $+70^\circ\text{C}$
- STORAGE TEMPERATURE RANGE (T_{STG}) -55 to $+125^\circ\text{C}$
- LEAD TEMPERATURE (DURING SOLDERING):
At distance $1/16 \pm 1/32$ in. (1.59 ± 0.79 mm) from case for 10 s max. $+265^\circ\text{C}$

OPERATING CONDITIONS at $T_A = 0$ to $+70^\circ\text{C}$

For maximum reliability, operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS			UNITS
	ALL TYPES			
	MIN.		MAX.	
DC Operating Voltage Range		4.5	5.5	V
Input Voltage Range	V_{IH}	2.2	$V_{DD} + 0.3$	
	V_{IL}	-0.3	0.8	
Input Signal Rise or Fall Time ^Δ	t_r, t_f	—	5	μs

^ΔInput signal rise and fall times with a duration greater than the maximum value can cause loss of stored data in the selected mode.**STATIC ELECTRICAL CHARACTERISTICS at $T_A = 0$ to $+70^\circ\text{C}$, $V_{DD} = 5\text{ V} \pm 10\%$, Except as noted**

CHARACTERISTIC	CONDITIONS	LIMITS			UNITS		
		ALL TYPES					
		Min.	Typ.*	Max.			
Standby Device Current	I_{DDS}	$CE1 = V_{IH}$ or $CE2 = V_{IL}$	—	1.5	3	mA	
	I_{DDSI}	$CE1 = CE2 \geq V_{DD} - 0.2\text{ V}$ or $CE2 \leq 0.2\text{ V}$	—	2	100		μA
Output Voltage Low Level	V_{OL} Max.	$I_{OL} = 2.1\text{ mA}$	—	—	0.4	V	
		$I_{OL} = 1\text{ }\mu\text{A}$	—	—	0.1		
Output Voltage High Level	V_{OH} Min.	$I_{OH} = -1\text{ mA}$	2.4	—	—	V	
		$I_{OH} = -1\text{ }\mu\text{A}$	—	$V_{DD} - 0.1$	—		
Input Leakage Current	I_{IN} Max.	$V_{IN} = 0\text{ V to } V_{DD}$	—	± 0.1	± 2	μA	
3-State Output Leakage Current	I_{OUT}	$V_{IO} = 0\text{ V to } V_{DD}$	—	± 0.5	± 2		
Operating Device Current	$I_{OPER1}^{\#}$	$V_{IN} = V_{IL}, V_{IH}$	$t_{CYC} = 1\text{ }\mu\text{s}$	—	4.5	9	mA
			$t_{CYC} = 120\text{ ns}$	—	22.5	45	
	$I_{OPER2}^{\#}$	$V_{IN} = 0.2\text{ V}, V_{DD} - 0.2\text{ V}$	$t_{CYC} = 1\text{ }\mu\text{s}$	—	2	4	
			$t_{CYC} = 120\text{ ns}$	—	20	40	
Input Capacitance	C_{IN}	$V_{IN} = 0\text{ V},$ $f = 1\text{ MHz}, T_A = 25^\circ\text{C}$	—	4	6	pF	
Output Capacitance	C_{IO}	$V_{IO} = 0\text{ V},$ $f = 1\text{ MHz}, T_A = 25^\circ\text{C}$	—	6	8		

*Typical values are for $T_A = 25^\circ\text{C}$ and nominal V_{DD} .[#]Outputs open circuited.

ศูนย์วิทยทรัพยากร
จุฬาลงกรณ์มหาวิทยาลัย



ประวัติผู้เขียน

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